

# Unintended gas breakdowns in narrow gaps of advanced plasma sources for semiconductor fabrication industry

*Willca Villafana<sup>1</sup>, Sung Hyun Son<sup>1</sup>, Geunwoo Go<sup>2</sup>, Igor D Kaganovich<sup>1</sup>, Alexander Khrabrov<sup>1</sup>, Hyo-Chang Lee<sup>3</sup>, Kyoung-Jae Chung<sup>4</sup>, Gwang-Seok Chae<sup>4</sup>, Seungbo Shim<sup>5</sup>, Donghyeon Na<sup>5</sup>, and June Young Kim<sup>6\*</sup>*

<sup>1</sup> Princeton Plasma Physics Laboratory, Princeton, NJ, USA

<sup>2</sup> Department of Nuclear Engineering, Seoul National University, Seoul, South Korea

<sup>3</sup> Department of Electronics and Computer Engineering, Korea Aerospace University, Goyang, South Korea

<sup>4</sup> Department of Semiconductor Science, Engineering and Technology, Korea Aerospace University, Goyang, South Korea

<sup>5</sup> Samsung Electronics Co. Ltd., Hwaseong, South Korea

<sup>6\*</sup> Department of AI Semiconductor Engineering, Korea University, Sejong, South Korea

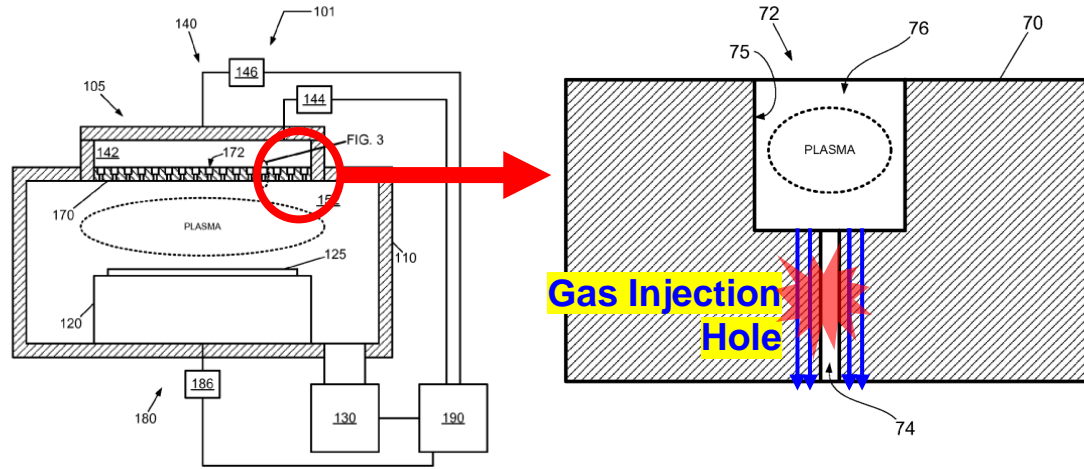
# Talk Overview

1. Context and motivation
2. Kinetic modeling via Particle-In-Cell simulation using EDIPIC-2D
3. Results and discussion
4. Modeling capabilities and expertise at PPPL via PCRFB

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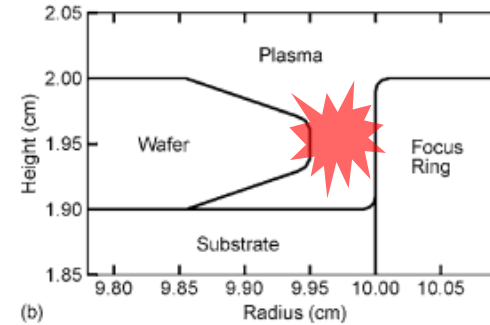
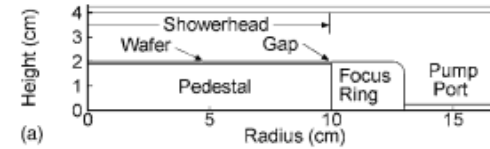
# Context and Motivation



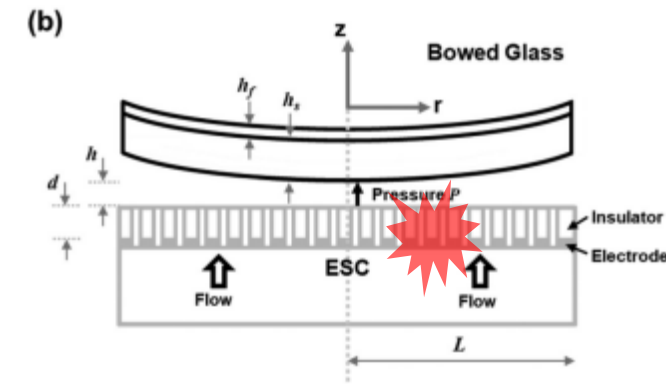
Processing chamber for ICP/CCP (left) and corresponding injection hole (right) [1]

Similar **narrow gap structures in various sources**, also could be vulnerable

**Consequences?**  
**Chamber lifetime, Reliability ↓**



Gap between focus ring and wafer (CCPs) [2]



Wafer backside cooling channel (CCPs/ICPs) [3]

[1] Chen Lee, and Lin Xu., U.S. Patent No. 7,744,720 (2010)

[2] N.Y. Babaeva, and M.J. Kushner, Journal of Applied Physics **101**(11), 113307 (2007)

[3] S. Park, *et al.*, Physics of Plasmas **28**(10), 103505 (2021)

# Context and Motivation

## Classical Paschen law

$$V_b = \frac{Bpd}{\left[ \ln(Apd) - \ln \left\{ \ln \left( 1 + 1 / \gamma_{SE} \right) \right\} \right]}$$

A,B : Gas dependent constants

$\gamma_{SE}$  : Ion induced SEE coefficient

→ Assumes 1D Townsend discharge

(Which is very simple)

More complex configuration



## Modified Paschen law[1]

Table 3. Representative studies of the modified Paschen curve.

Author	Research method	Features	Gas	Pressure (Torr)	Gap (mm)	Configuration
Lisovskiy <i>et al</i> (reference [58])	Experimental	Long tube discharge	N <sub>2</sub> , O <sub>2</sub> , Ar, air	0.01–10	5–100	Plane to plane (diameter: 9–100 mm)
Lisovskiy <i>et al</i> (reference [93])	Experimental and theoretical	Non-uniform electric field	N <sub>2</sub>	0.05–100	3–300	Plane to plane (diameter: 12 mm)
Schoenbach <i>et al</i> (reference [99])	Experimental discharge	Hollow cathode	Ar	56–896	0.25	Plane to hollow (hollow hole diameter: 0.2–0.7 mm)
Xu <i>et al</i> (reference [133])	Experimental and theoretical	Anisotropic scattering and fast atoms of ions	He	N/A (0.35 < pd (Torr cm) < 0.6)	14	Plane to plane (diameter: 150 mm)
Meng <i>et al</i> (reference [120])	Experimental and theoretical	Pulsed discharge	Air	760	0.001–0.025	Sphere to sphere
Brayfield <i>et al</i> (reference [123])	Experimental	Electrode–surface condition	Air	760	0.001–0.01	Pin to plate
Marić <i>et al</i> (reference [124])	Experimental electrode	Asymmetric	Ar	N/A (0.1 < pd (Torr cm) < 6)	0.5–1.5	Plane to step or central hole
Torres and Dhariwal (references [107, 108])	Experimental dominated discharge	Field emission	Air	0.3–760	0.0005–0.025	Sphere to plane, cylinder to plane
Go <i>et al</i> (reference [35])	Theoretical	Independent treatment of field emission and secondary emission	Air	760	0.003–0.02	Plane to plane
Lisovskiy and (reference [27])	Experimental and theoretical	RF voltage amplitude within the range 0–1000 V	H <sub>2</sub> , Ar, air	0.01–20	6.5–70	Plane to plane (diameter of 5–100 mm)
Moon <i>et al</i> (reference [79])	Experimental	Driving frequencies in the range 1.86–27.1 MHz	Helium	760	3	Plane to plane (diameter of 60 mm)

**Narrow gap breakdown even more complex; e.g., presence of background plasma**

**We conduct experiments and simulations to investigate the breakdown**

[1] J.Y. Kim, *et al.* Plasma Sources Sci. Technol. **31**(3), 033001 (2022)

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# Our PIC code EDIPIC 2D

Use of EDIPIC-2D code, based on earlier 1D version [1]

- ✓ Comprehensive 2D Cylindrical/Cartesian explicit PIC code.
- ✓ State-of-the art collision models. FFT methods or PETSc library for Poisson solver. External circuits. Inner objects
- ✓ Verified in international benchmarks [1,2,3,4]
- ✓ Numerous users from academia and industry

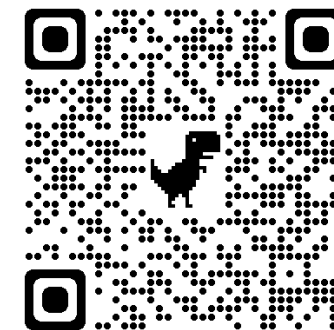
**More info at poster session!**



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**Open source and portable code able to simulate a wide variety  
of low temperature plasma physics problems**

<https://github.com/PrincetonUniversity/EDIPIC-2D>



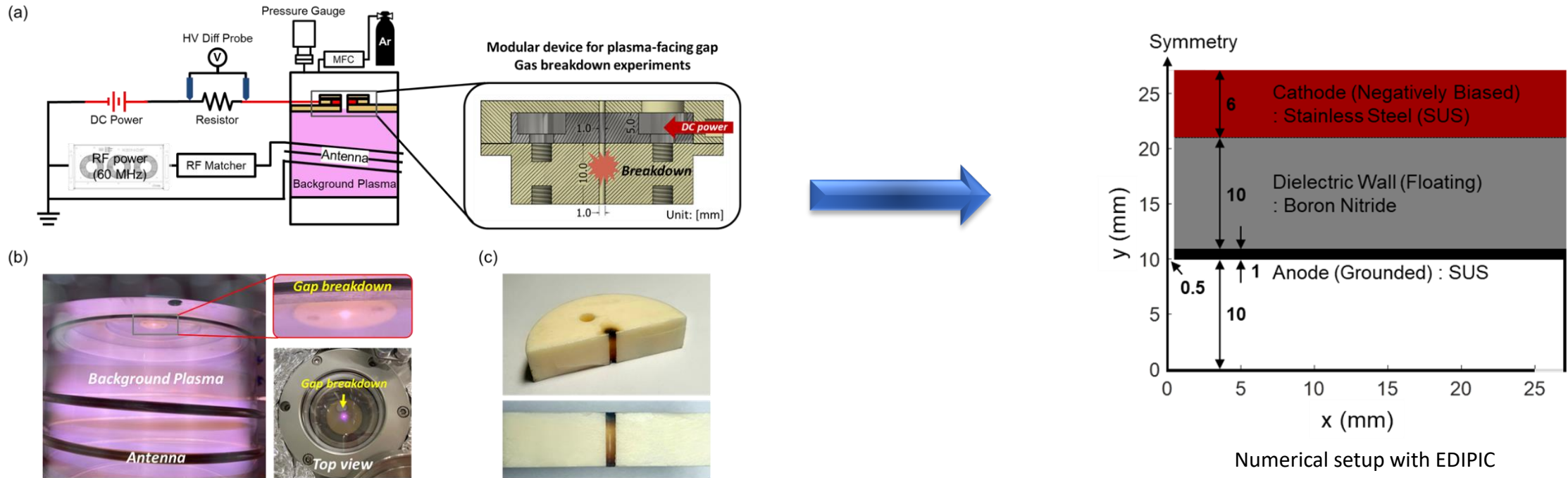
[1] Sydorenko, PhD thesis, (2006)

[2] T. Charoy, *et al.*, Plasma Sources Sci. Technol. 28(10), 105010 (2019).

[3] W. Villafana *et al.*, Physics of Plasmas **30**(3), 033503 (2023)

[4] M.M. Turner *et al.*, Physics of Plasmas 20(1), 013507 (2013).

# Configuration and numerical setup [1]



Experimental setup performed at SNU. (a) ICP schematic. (b) Breakdown during operation (c) inner surface after several discharges.

- ✓ Electron-induced Secondary Electron Emission is based on Vaughan's model [2]
- ✓ Ion-induced Secondary Electron Emission
- ✓ Initial conditions: Uniform Argon plasma, density  $n_0$ , Maxwellian distribution, temperatures  $T_{e,0}$  &  $T_{i,0}$
- ✓ Bias cathode voltage  $V_{cat}$

[1]S.H. Son, *et al.* Applied Physics Letters **123**(23), 232108 (2023)

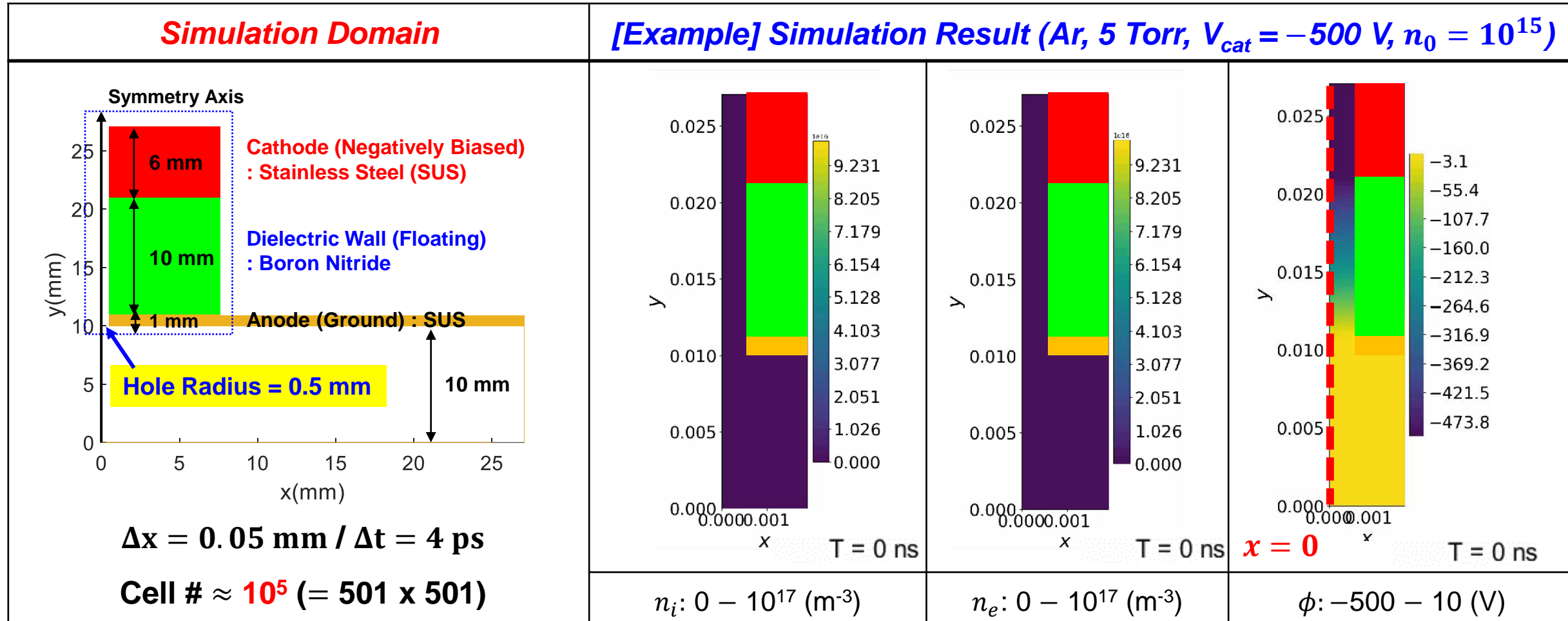
[2]J.R.M. Vaughan, IEEE Trans. Electron Devices **36**(9), 1963–1967 (1989)



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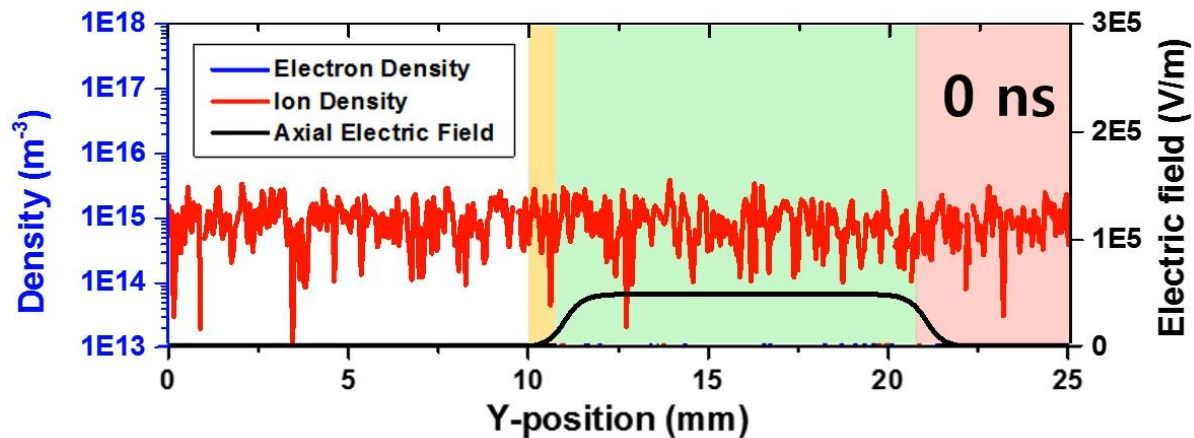
# 2D results when breakdown occurs



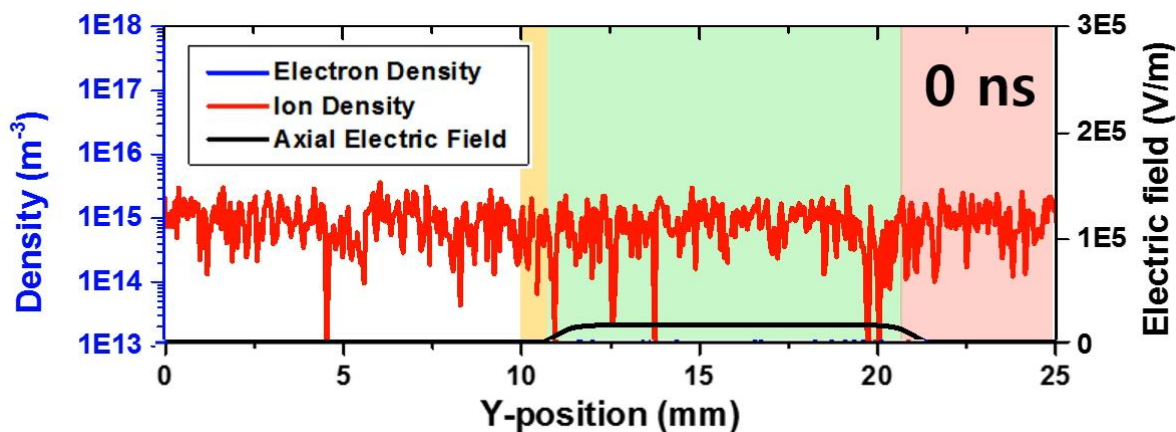
- Dramatic increase of the plasma density, the potential is screened out
- Propagation of the breakdown inside the hole

# 1D results at centerline $x = 0$

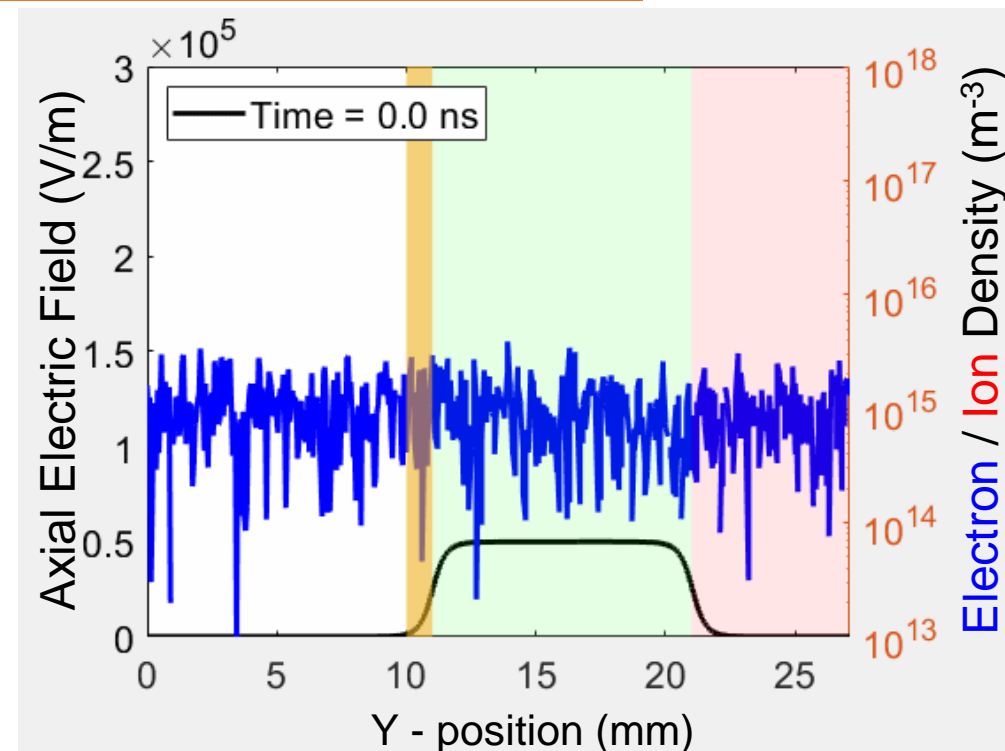
$V_{cat} = -500V$ :breakdown



$V_{cat} = -150V$ :No breakdown



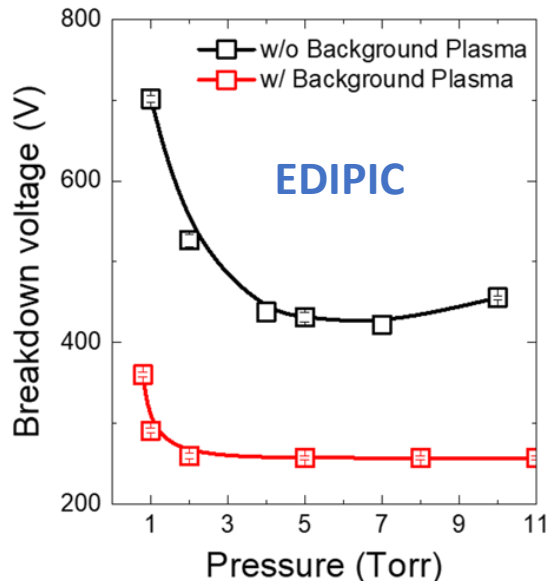
1D cuts at  $x = 0$  with  $P_n = 5$  Torr,  $n_0 = 10^{15} m^{-3}$



$P_n = 5$  Torr,  $n_0 = 10^{15} m^{-3}$   $V_{cat} = -500V$

- An insufficient bias voltage does not trigger an electron avalanche
- Breakdown criterion:  $n_i \uparrow + n_i \approx n_e$

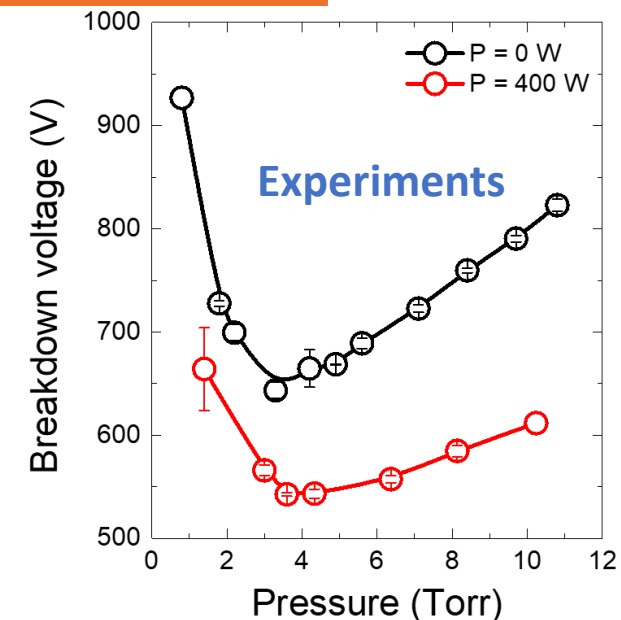
# Final Paschen curve



➤ Presence of background plasma lowers breakdown voltage: particle leakage distorts local E field and enhances ionization

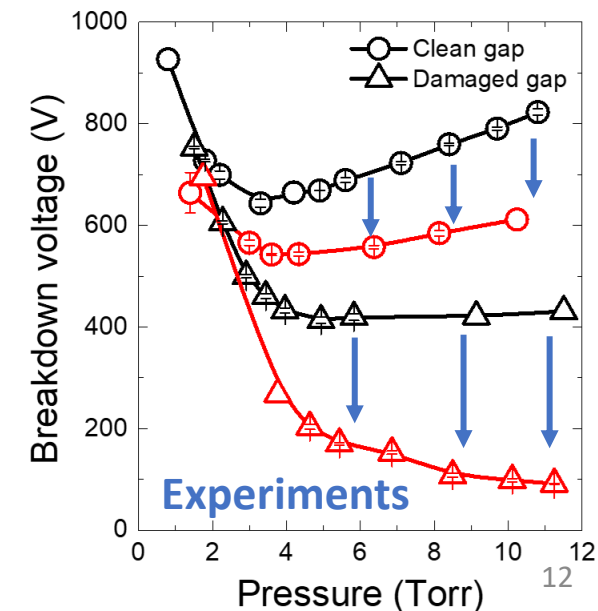
➤ The trend of breakdown voltage in both EDIPIC and experiments is similar despite key differences:

- Cartesian vs Cylindrical
- BN vs Al<sub>2</sub>O<sub>3</sub>



Further study in progress with Cylindrical in EDIPIC + Alumina data

- Damaged gap = gap with previous breakdowns
- Crucial to prevent first breakdown from happening



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**More info at poster session!**

# Our Development Team

**Igor D. Kaganovich, PI management, benchmarking, physics models**



## LTP-PIC:

- **Stéphane Ethier, co-PI** porting the code to Heterogeneous CPU/GPU architectures.
- **Andrew (Tasman) Powis:** 3<sup>rd</sup> year postdoc, main LTP code developer.



## 2D EDIPIC:

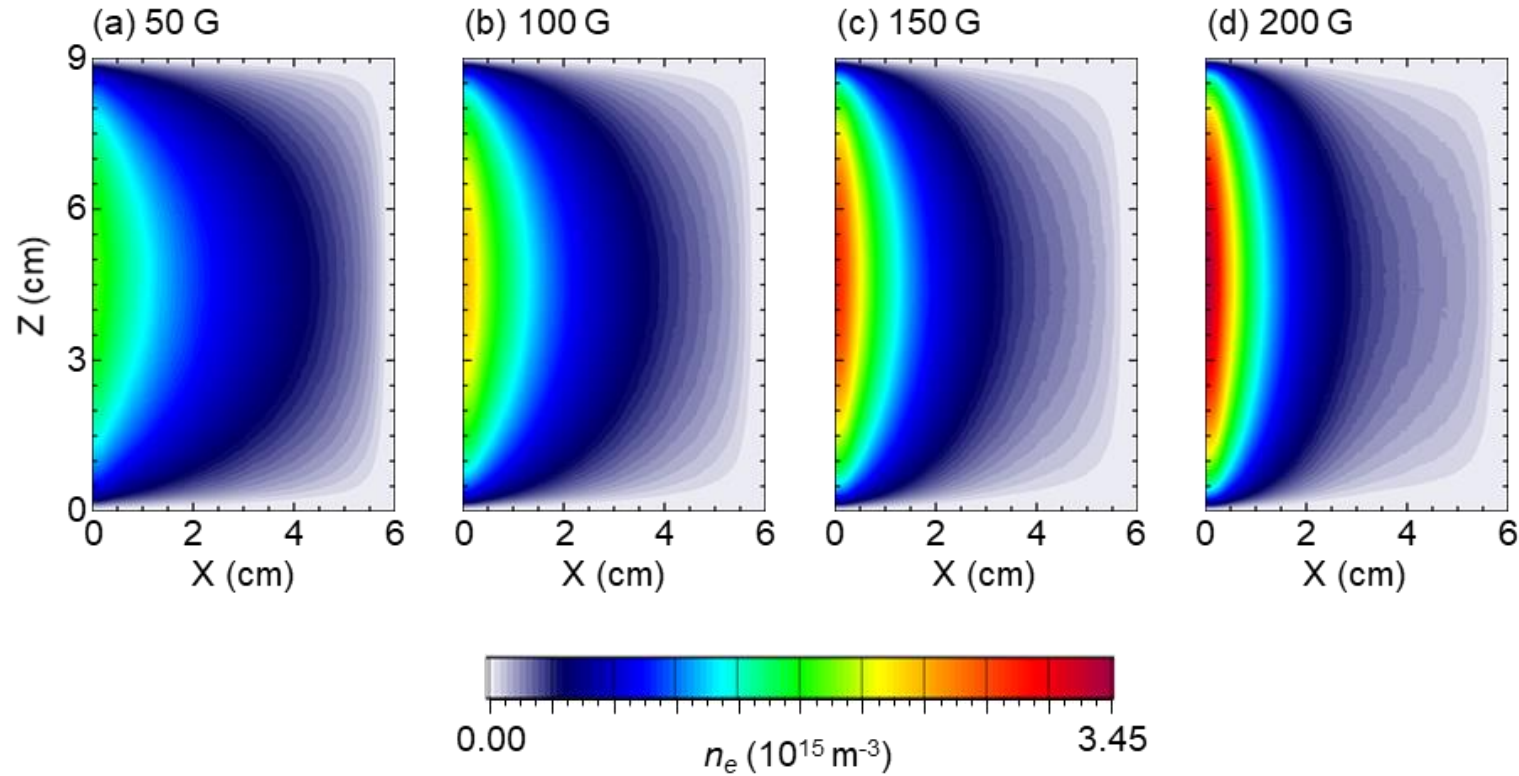
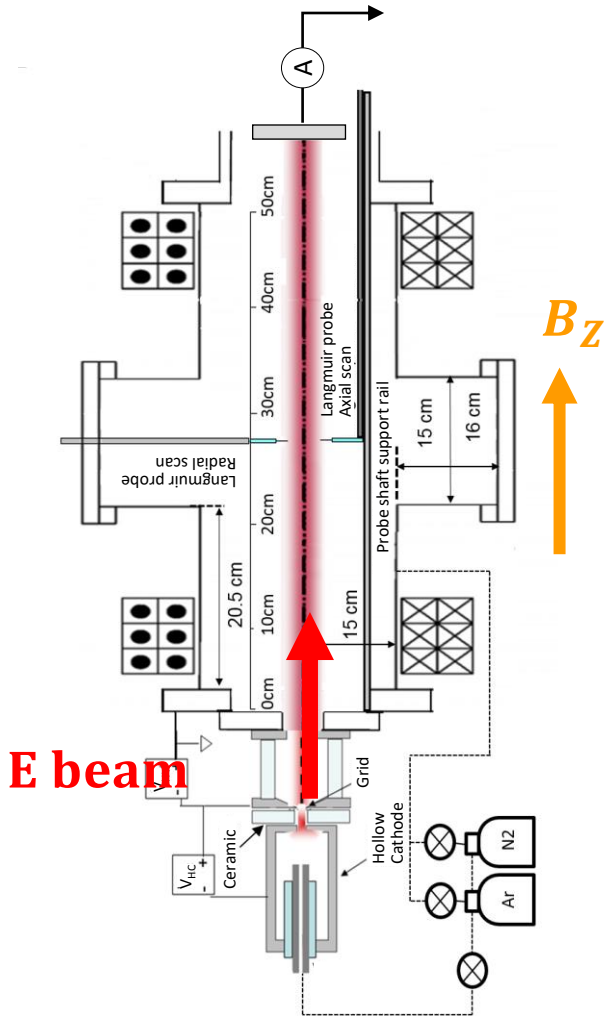
- **Dmytro Sydorenko** Univ. of Alberta, original developer of EDIPIC since his Ph.D. thesis.
- **Alex Khrabrov, contractor.**
- **Willca Villafana** 2<sup>nd</sup> year postdoc



# Electron-beam-generated plasma

10 – 40 mTorr gas pressure  
0 – 200 G magnetic field

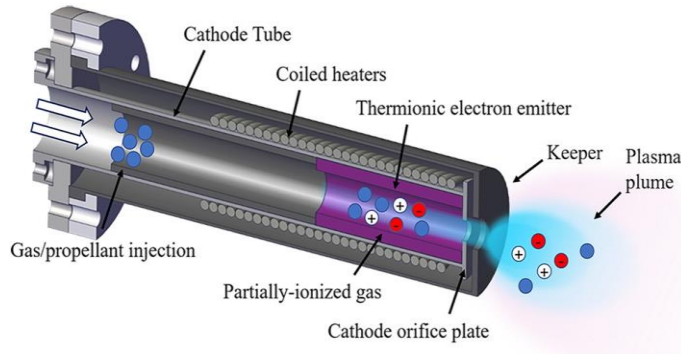
$n_e$



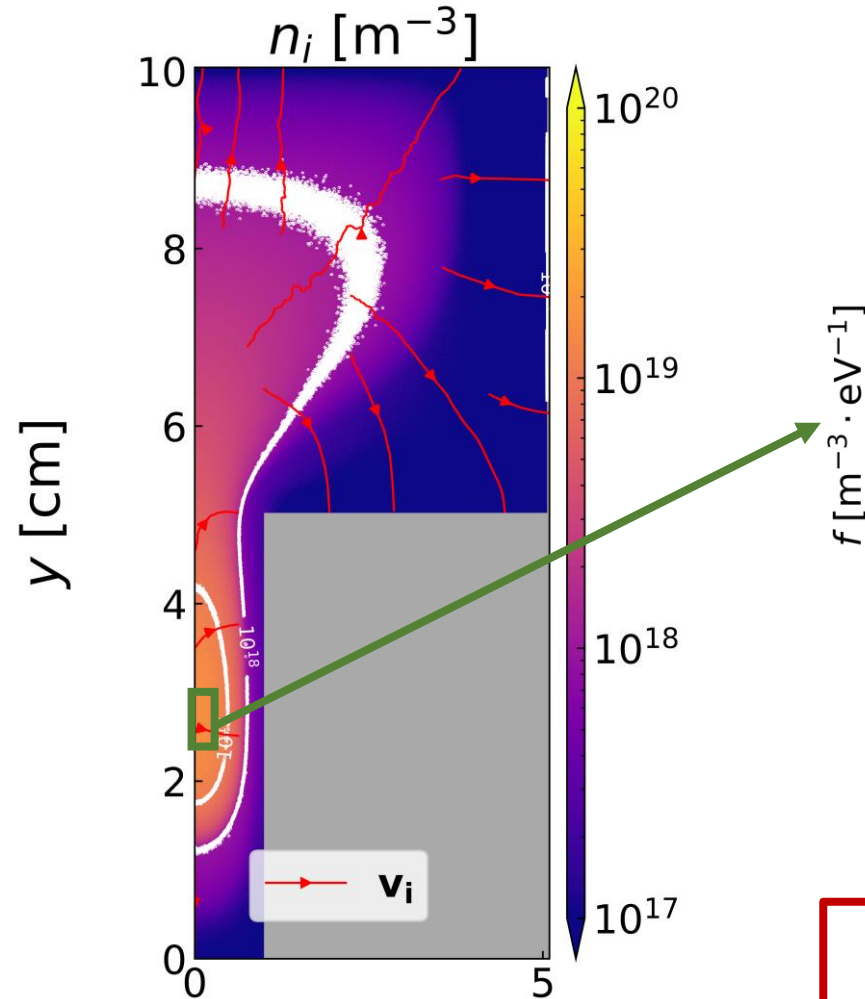
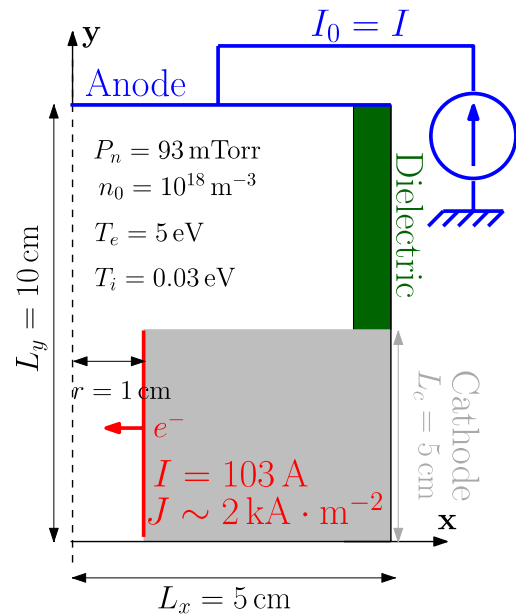
Schematic of NRL experimental set up Ar, 20 mT, xx G, 12.5 mA/m, 2 keV electron beam

<sup>1</sup> S. Rauf, D. Sydorenko, S. Jubin, W. Villafana, S. Ethier, A. Khrabrov, and I. Kaganovich, "Particle-in-cell modeling of electron beam generated plasma," Plasma Sources Sci. Technol. **32**(5), 055009 (2023).

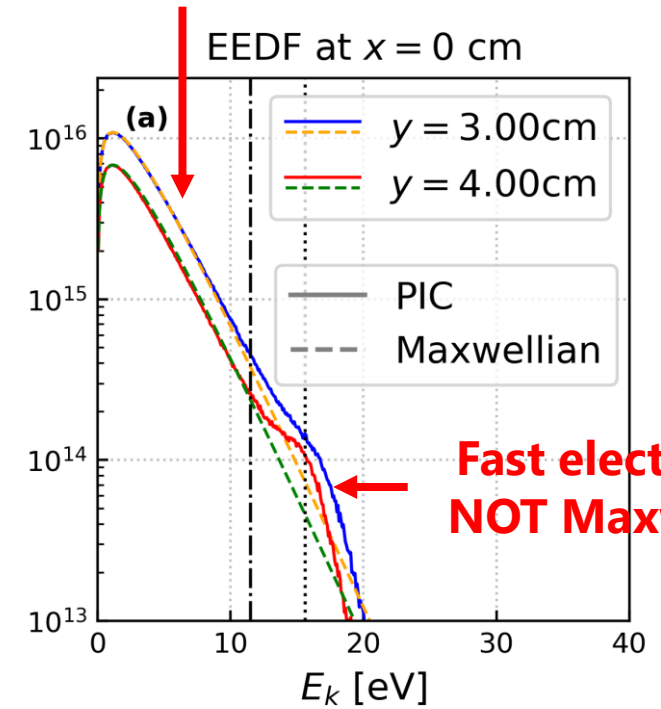
# Hollow cathode system



Schematic of hollow cathode [1]



**Maxwellian**



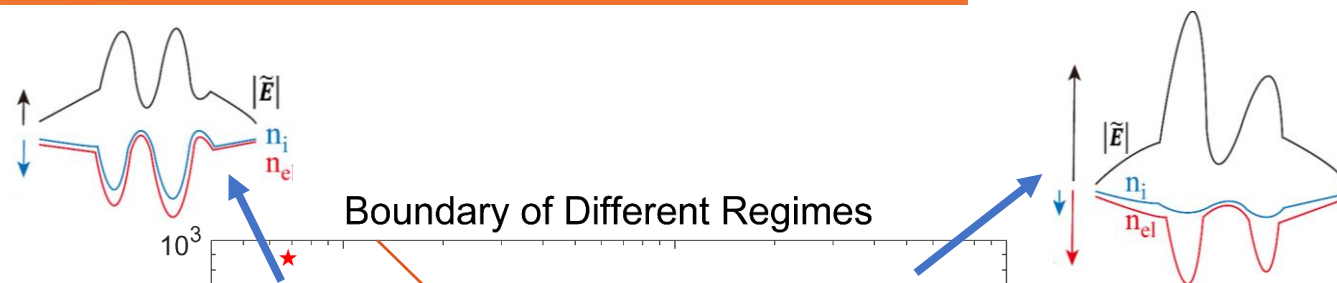
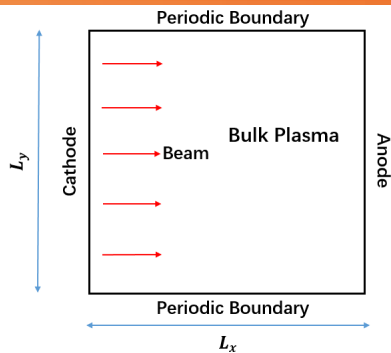
**Fast electrons = NOT Maxwellian**

Hollow cathode exhibits non Maxwellian EEDF



# Electron-beam plasma interaction

57 PIC simulations varying energy and density of the beam  $E_b$  and  $n_b$

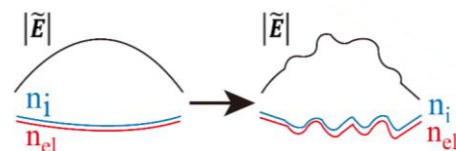
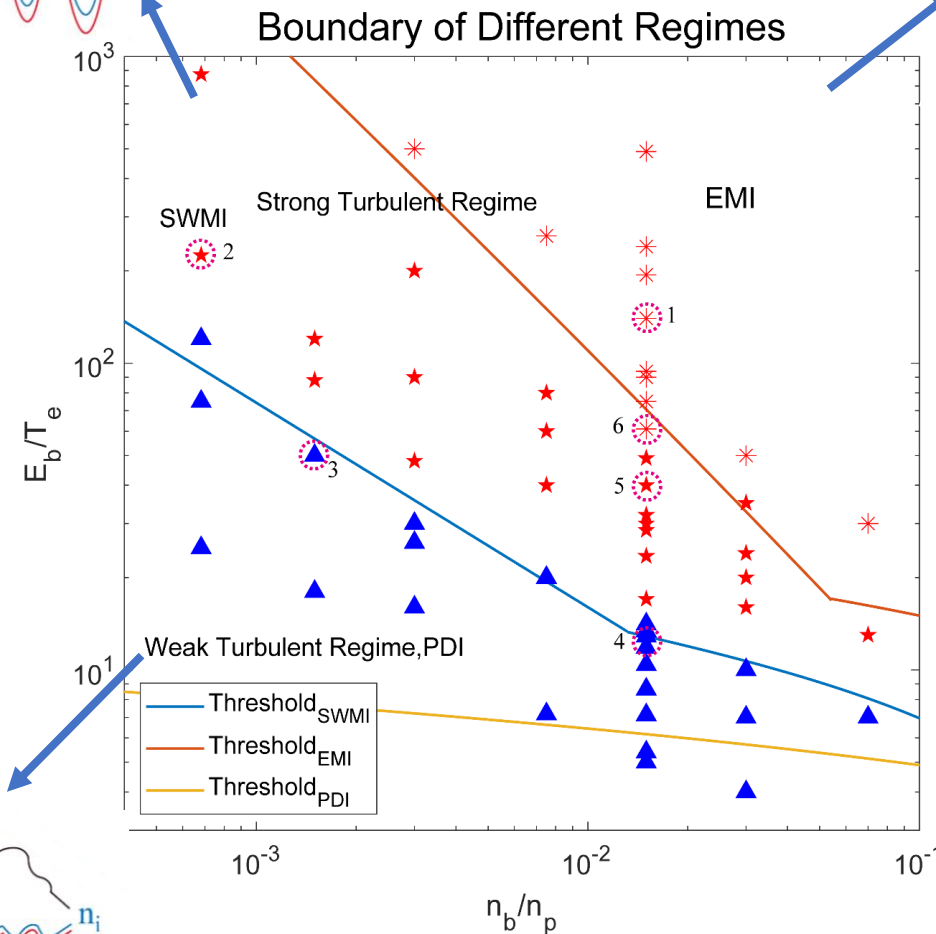


**PDI** (parametric decay instability): generating backward waves (waves slightly perturb plasma)

**SWMI** (standing wave modulational instability): localized standing waves

**EMI** (*electron modulational instability*): rapidly growing standing waves (breaks quasineutrality).

**NEW**



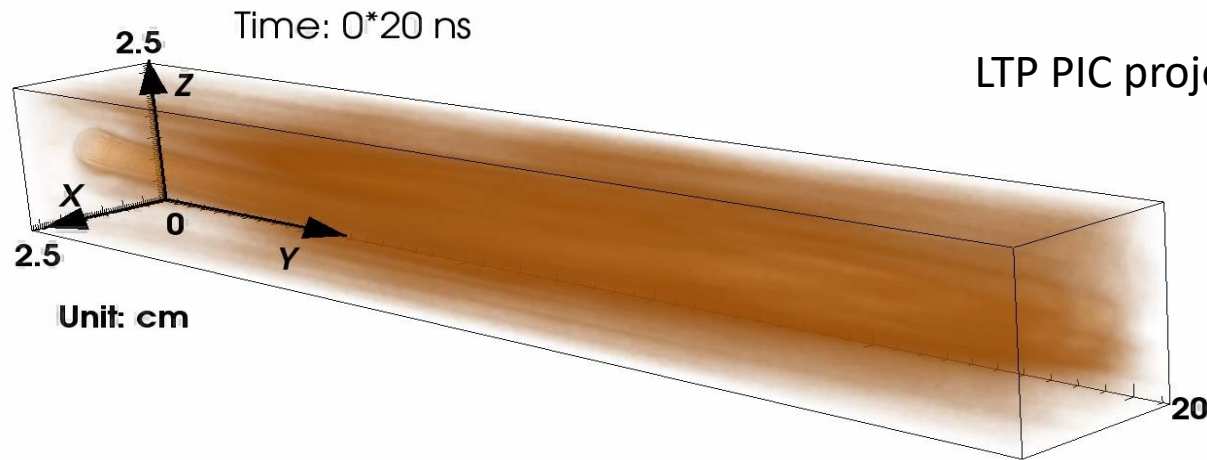
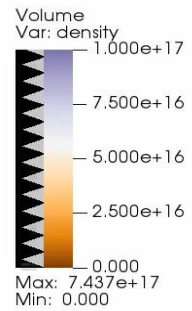
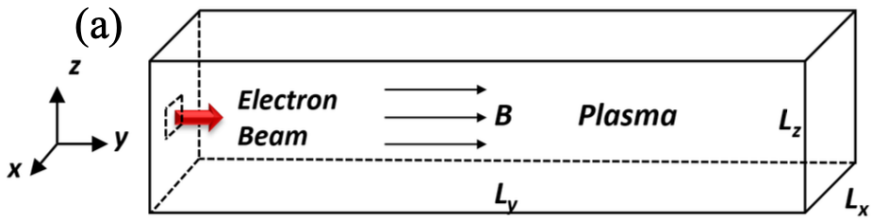
# Our PIC code LTP PIC

- Main features
  - ✓ Explicit 2D-3D/3V electrostatic PIC in uniform cartesian geometry
  - ✓ Written in C-C++, runs on CPUs **accelerated with GPUs** via OpenAcc
  - ✓ Monte-Carlo model of electron-neutral and ion-neutral collisions
  - ✓ Field solve via Geometric Multigrid algorithms from the Hydre package (LLNL)
  - ✓ Python + *VisIt* software as post-processing tools
- Written from the ground up for scalability:
  - ✓ Inter-node parallelization via *MPI*
  - ✓ Intra-node parallelization via *MPI* and/or *OpenMP*
  - ✓ Elimination of inner loop logic to take advantage of vector registers

Portable code and soon available to the community to simulate large 2D/3D simulation domains

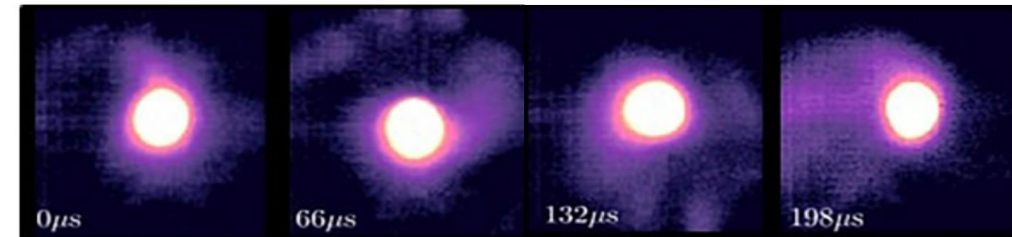
# 3D spoke-like activity in a Penning discharge

Partially magnetized ExB discharges, widely used in industry and research, often exhibit large-scale, low-frequency, coherent structures known as "spokes" [1,2].

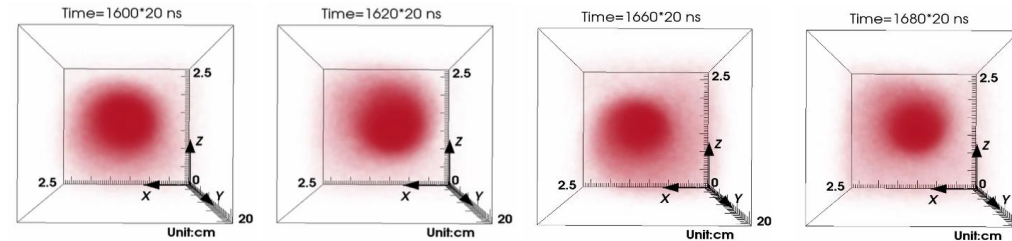


Experiments [1]

The experiments exhibit qualitatively similar behavior, with a rotation velocity similar to that observed in experiments.



LTP PIC projection



[1] E. Rodriguez, et al. Physics of Plasmas 26, 053503 (2019).

[2] A. Escarguel, The European Physical Journal D 56, pg. 209-214 (2010).  
 unintended gas breakdowns in narrow gaps of advanced plasma sources for semiconductor fabrication industry

# Conclusion



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- ✓ **Breakdown:** experimental and PIC study (**PCRF**). Background plasma and previous breakdowns facilitate future breakdowns
- ✓ **EDIPIC-2D** is an **open source extensively verified** PIC code routinely used by the industry and academia for a wide variety of LTP systems. Example of applications: **CCP, ICP, e-beam, hollow cathode, ECR, Hall thruster, Penning discharge, etc ... Realistic configuration with external circuit and inner objects. 10+ publications**
- ✓ **LTP-PIC** is a 2D/3D PIC designed for HPC aiming for whole-device modeling. **Excellent scalability up to hundreds of GPUs for large and more realistic geometries.**

# Questions?



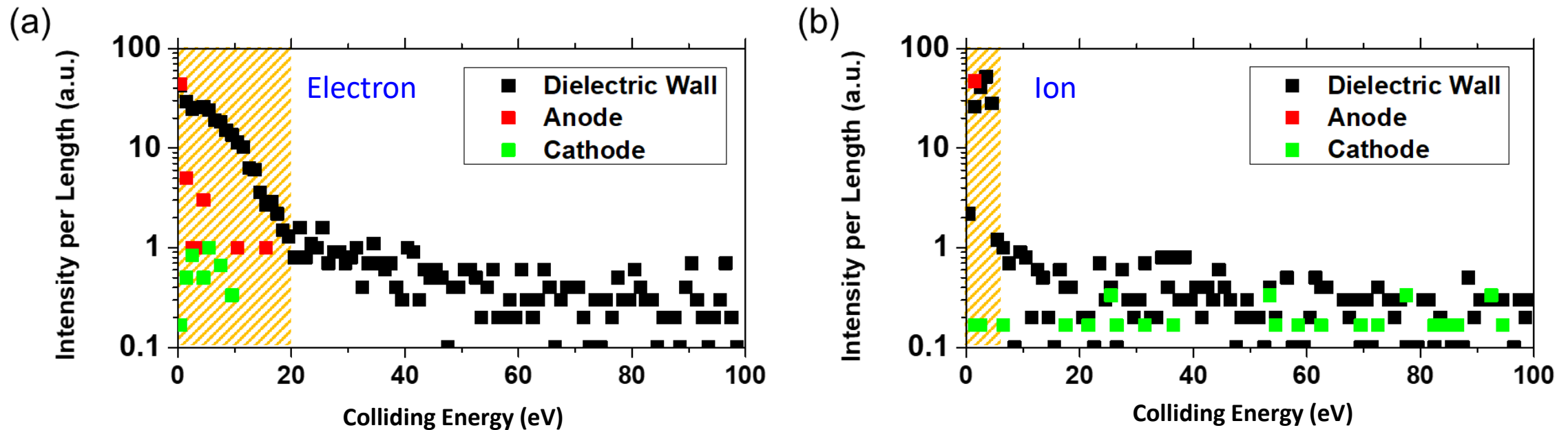
**More info at poster session!**

# Questions?

# Analysis of SEE: the $\gamma$ process

- Recorded normalized energy spectrum of particles hitting the walls

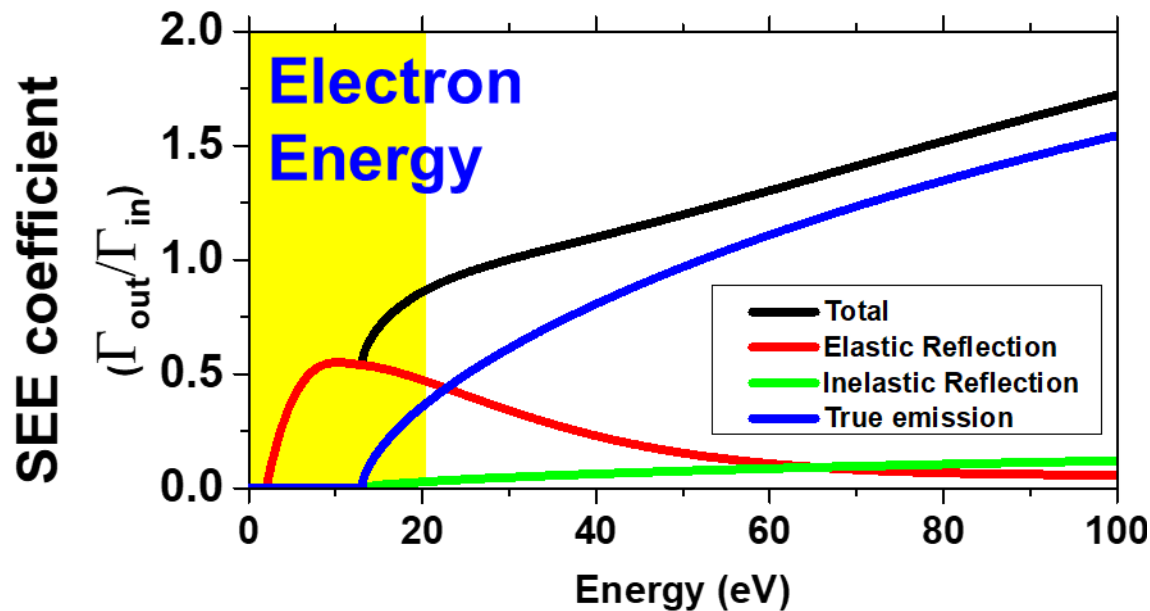
$$n_0 = 10^{15} \text{m}^{-3}, V_{cat} = -500 \text{V}$$



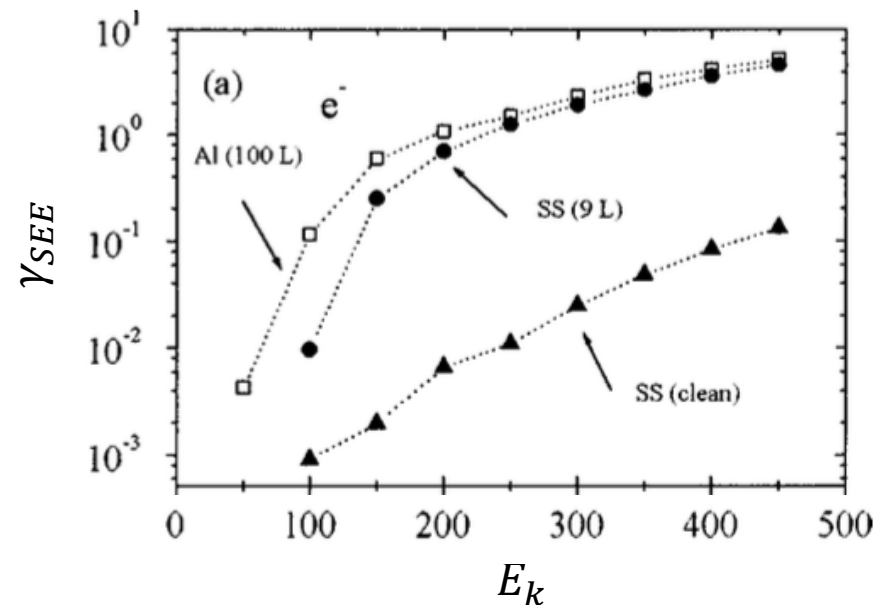
- Most electrons and ions hit the dielectric at low energy

# Analysis of SEE: the $\gamma$ process

- Electron-induced SEE yield for BN is based on the fitted Vaughan's model [1,2]



- Ion-induced SEE yield from stainless steel is below  $<0.1$  [3,4]



- A significant portion of SEE electrons is incident electrons reflected **elastically**
- Ion-induced SEE electrons from the cathode are less important in contrast to what is typically reported in the literature [5]

[1] D. Sydorenko, PhD thesis (2006)

[2] M. Villemant, *et al.* EPL **127**(2), 23001 (2019).

[3] A.V. Phelps, and Z.L. Petrovic, Plasma Sources Sci. Technol. **8**(3), R21–R44 (1999)

Unintended gas breakdowns in narrow gaps of advanced plasma sources for semiconductor fabrication industry

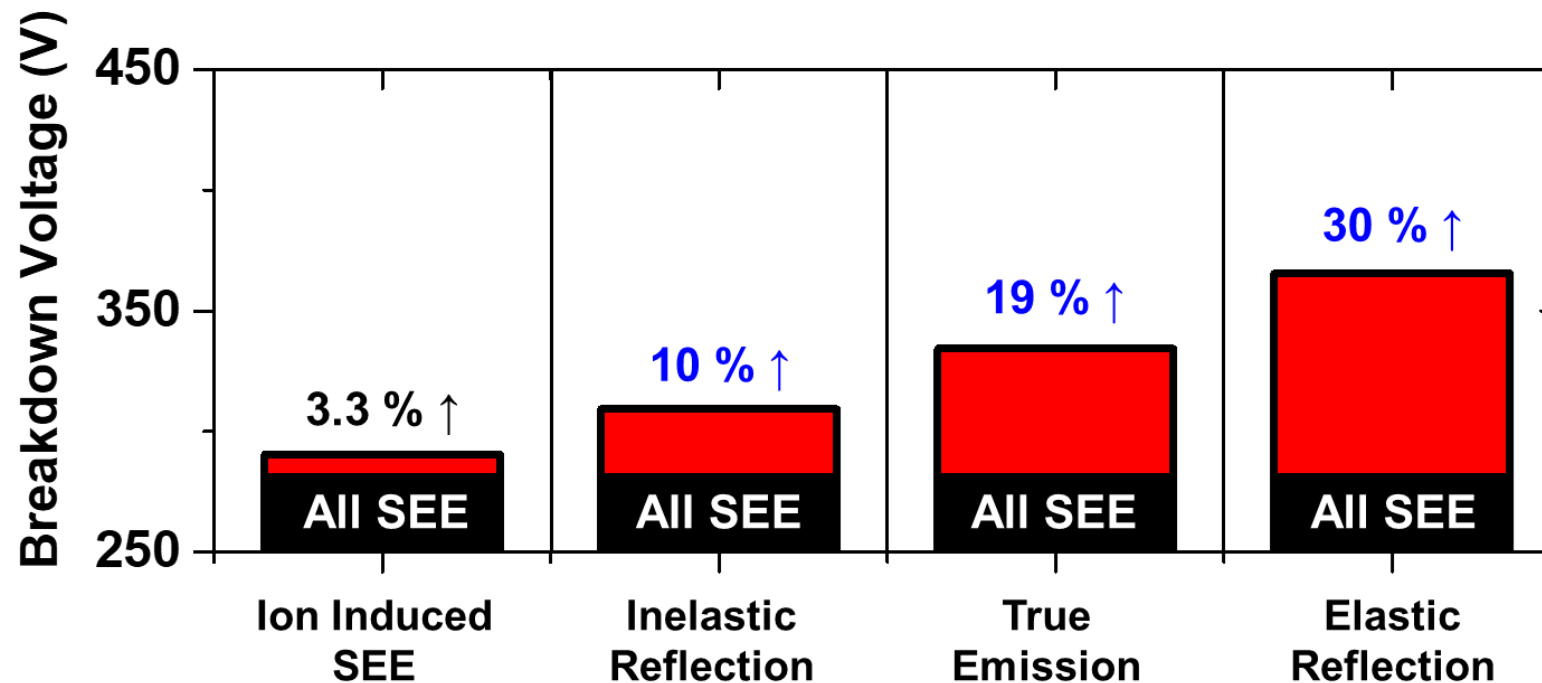
[4] S.G. Walton, *et al.*, Journal of Applied Physics **85**(3), 1832–1837 (1999)

[5] J.Y. Kim, Plasma Sources Sci. Technol. **31**(3), 033001 (2022)



# Analysis of SEE: the $\gamma$ process

- Variation of the breakdown voltage if the SEE yield is turned off

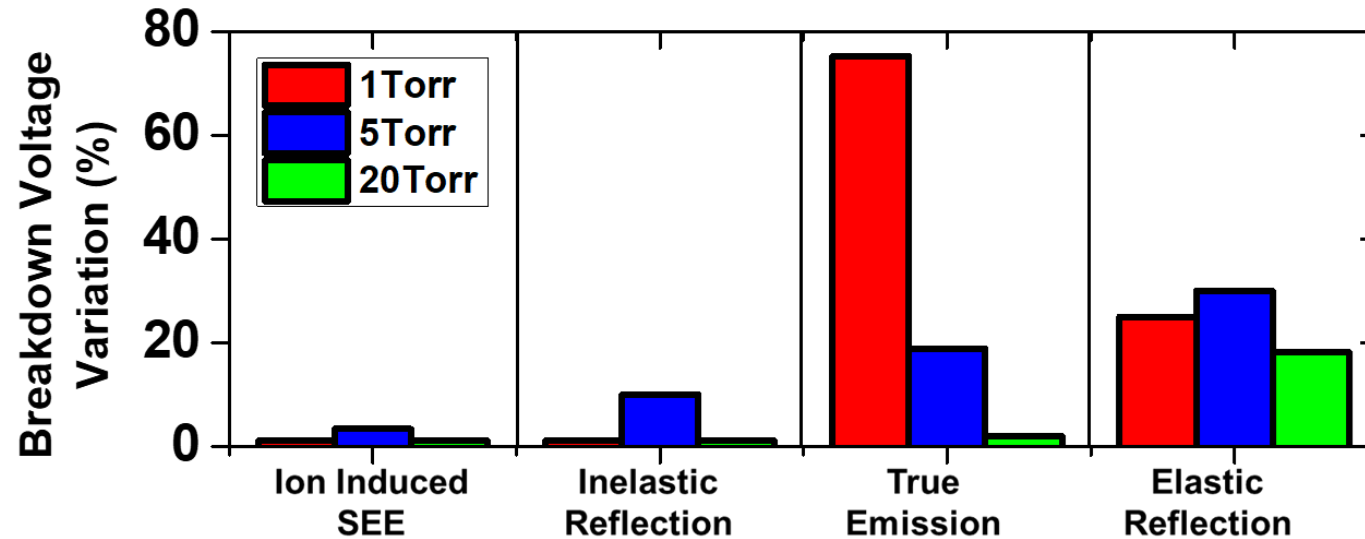


E.g., if elastic reflection in SEE is turned off,  $V_{breakdown}$  goes up by 30% with respect to the baseline ("All SEE")

- True SEE and Elastic Reflection are the most important

# Analysis of SEE: the $\gamma$ process

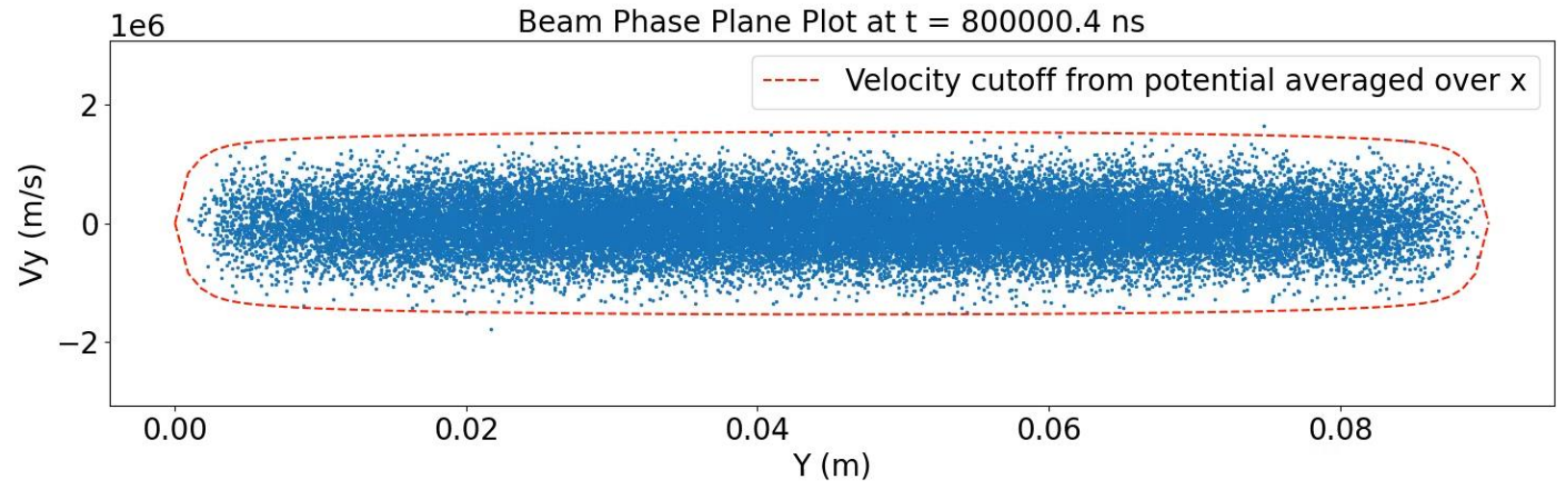
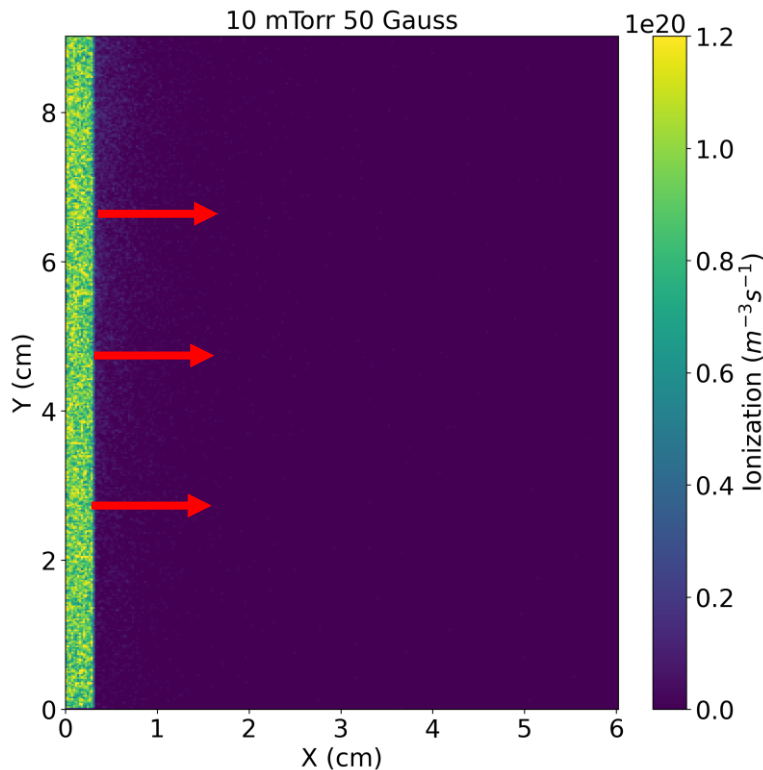
- Variation of breakdown voltage if SEE yield is turned off is dependent on pressure



- True SEE more important at low pressure because electrons are faster (less collisions)

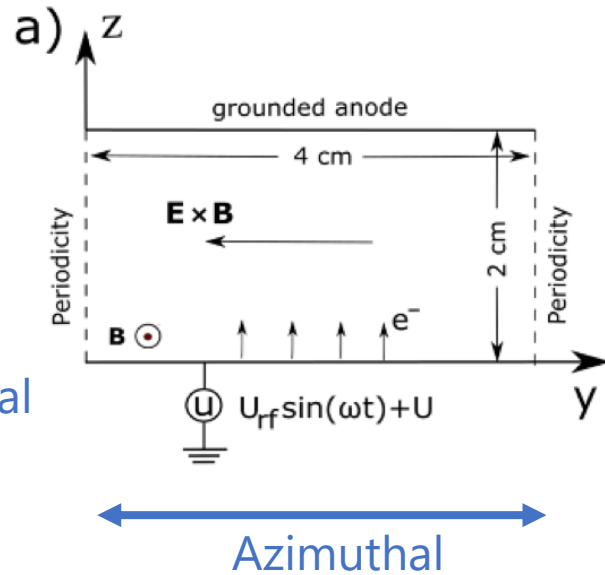
# Electron-beam-generated plasma

- The ionization zone is confined to the beam area

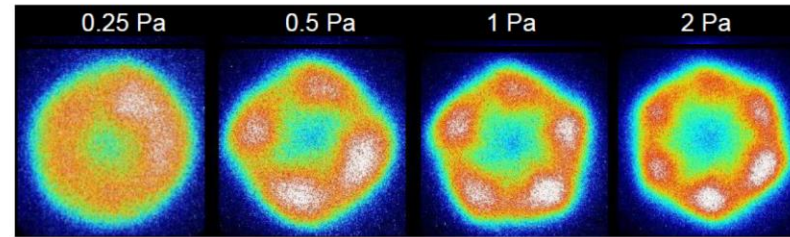


- Cold electrons are trapped in potential well. Fast, 2keV electrons escape
- Non ambipolar diffusion in  $x$  direction

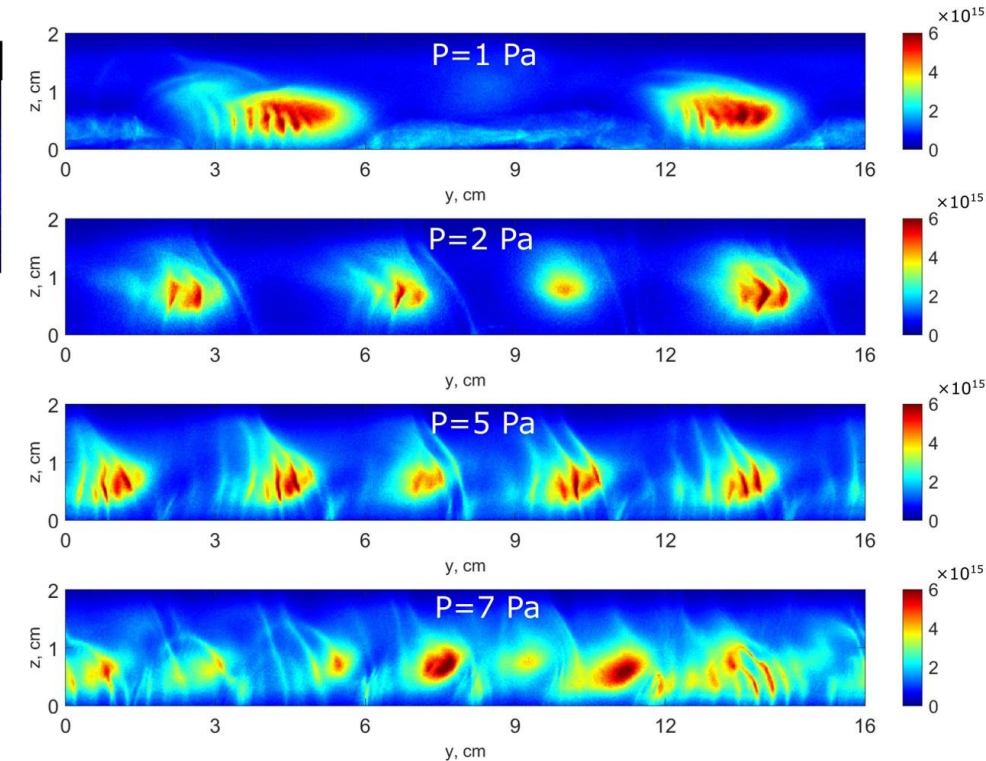
# Rotating spokes in RF CCP



Experiments



EDIPIC results

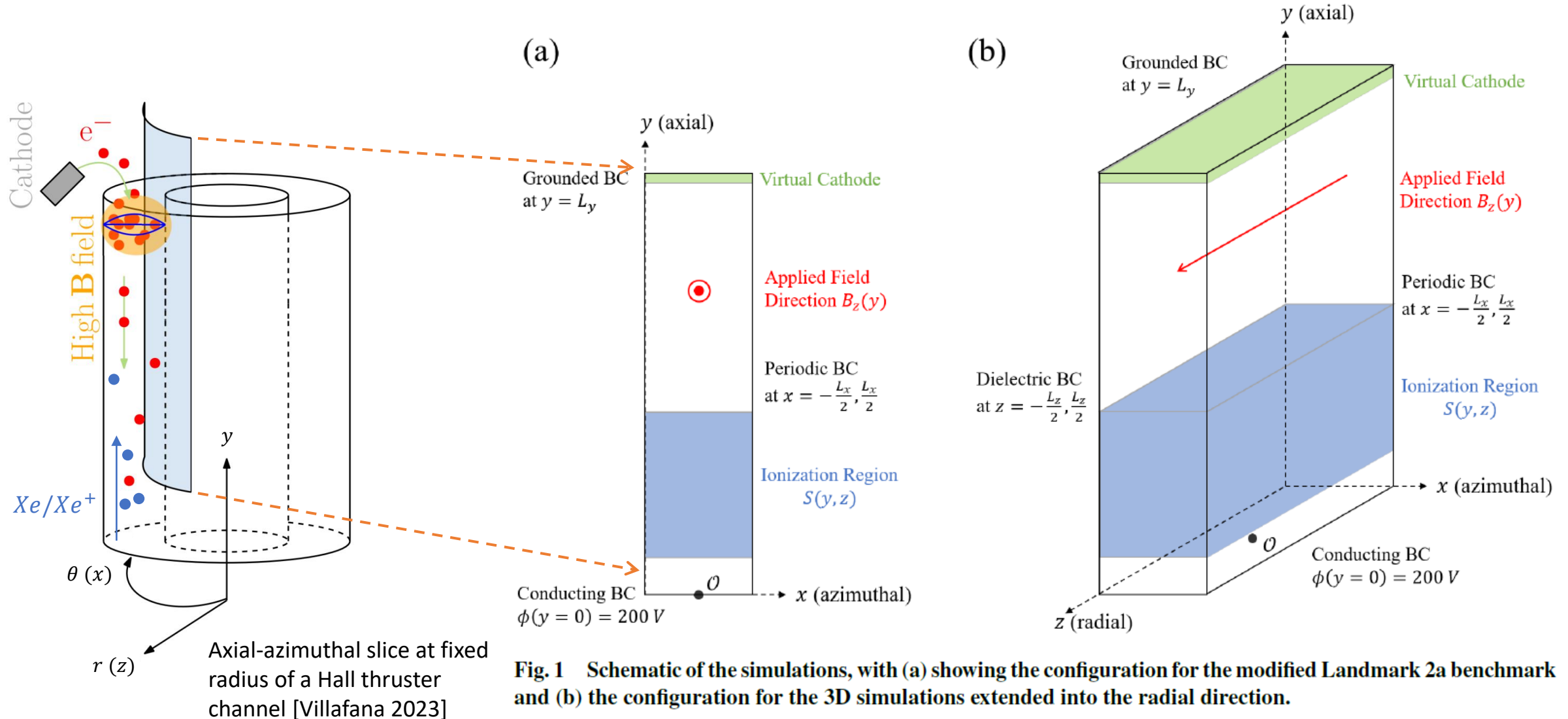


Similar trend in both PIC and experiments.

# Talk Overview

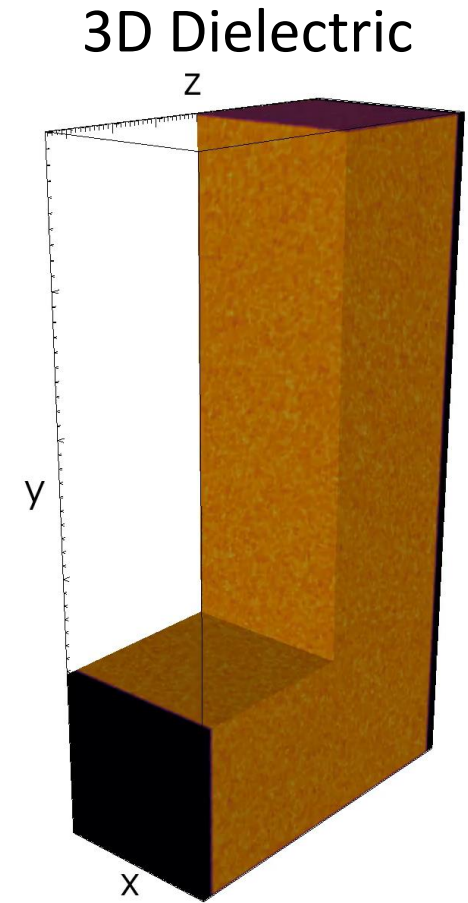
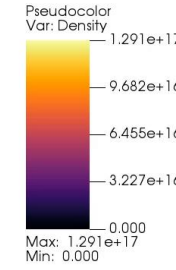
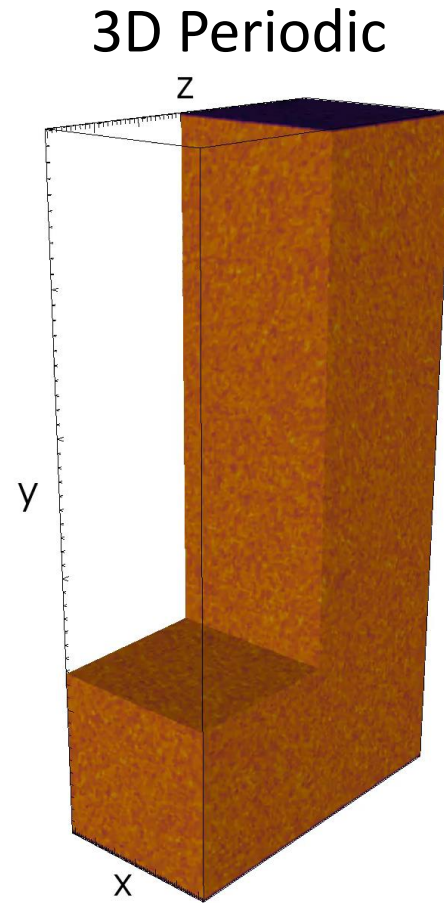
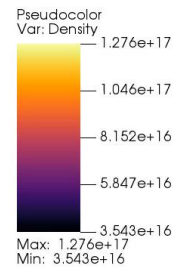
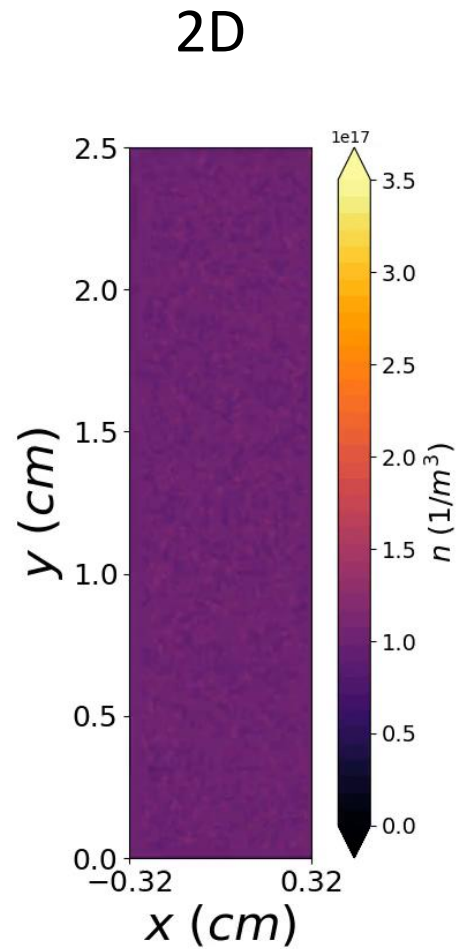
1. Context and motivation
2. Modeling capabilities using EDIPIC-2D
3. Toward 3D whole-device modelling with LTP-PIC
4. Advanced algorithms

# 3D simulation of Hall thruster channel



**Fig. 1** Schematic of the simulations, with (a) showing the configuration for the modified Landmark 2a benchmark and (b) the configuration for the 3D simulations extended into the radial direction.

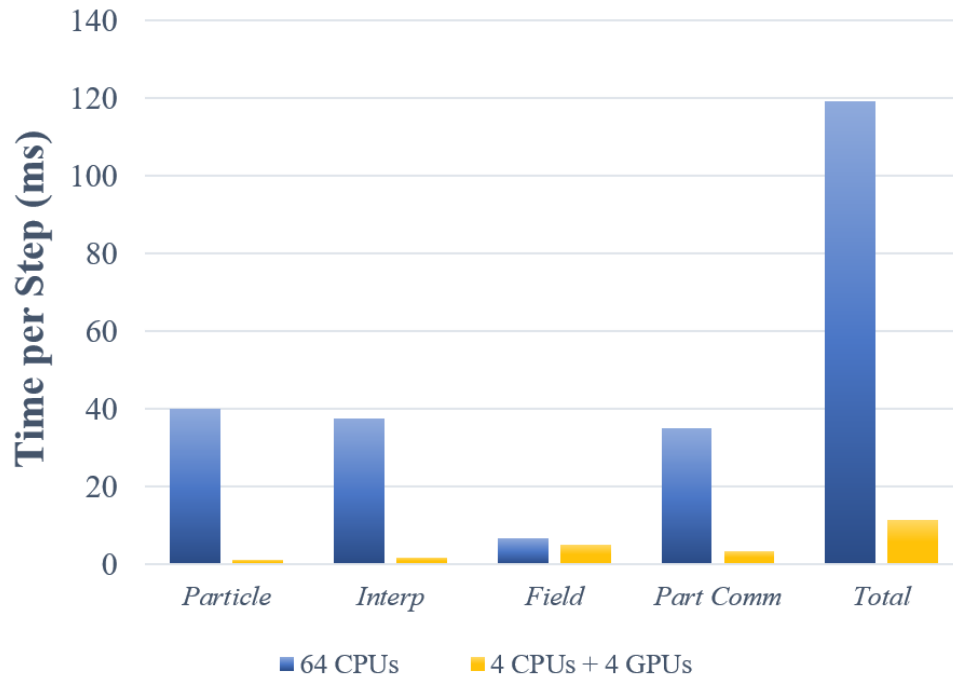
# 3D simulation of Hall thruster channel



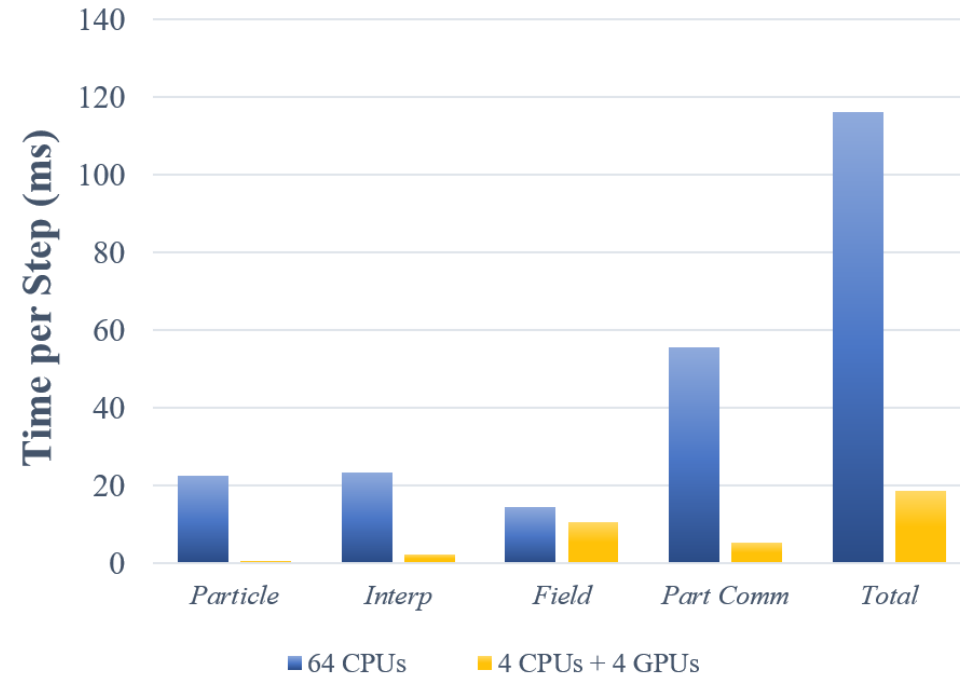
Different electron transport in 3D.  
Influence of boundary conditions

# Performance of LTP PIC

2D simulations  
8,192<sup>2</sup> cells with  
1,000 particles-per-cell  
256 nodes



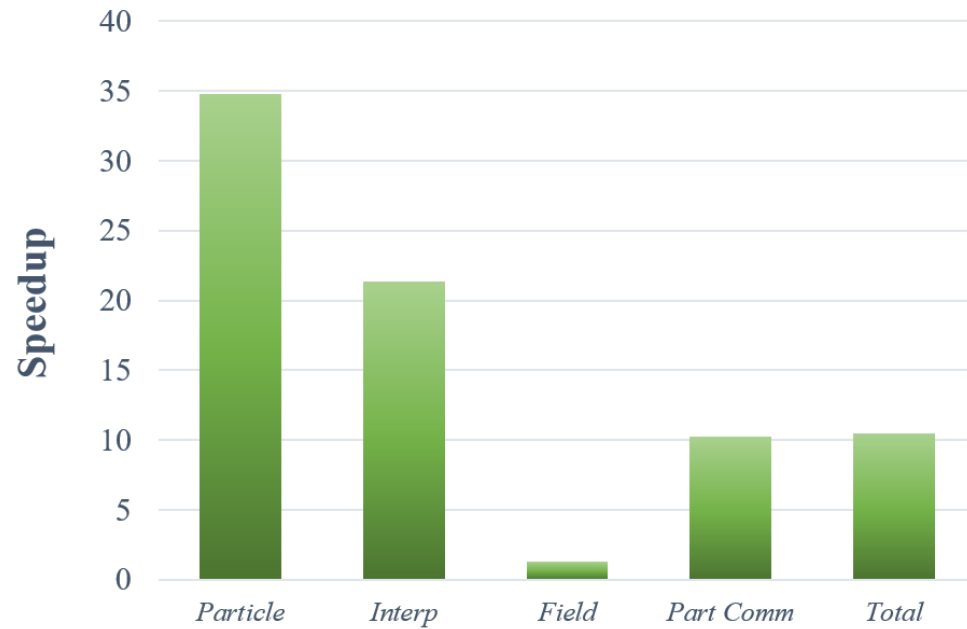
3D simulations  
256<sup>3</sup> cells with 1,000  
particles-per-cell  
128 nodes



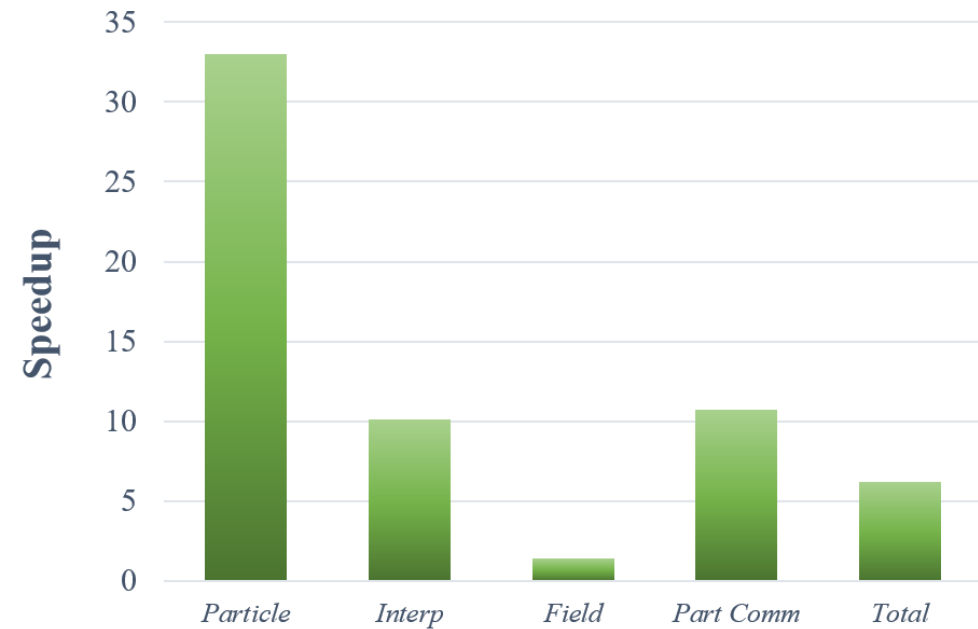


# Performance of LTP PIC

2D simulations  
8,192<sup>2</sup> cells with  
1,000 particles-per-cell  
256 nodes



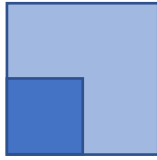
3D simulations  
256<sup>3</sup> cells with 1,000  
particles-per-cell  
128 nodes



# Performance of LTP PIC

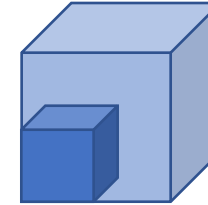
Weak scaling = load on resources remains the same while increasing the size of the domain

2D

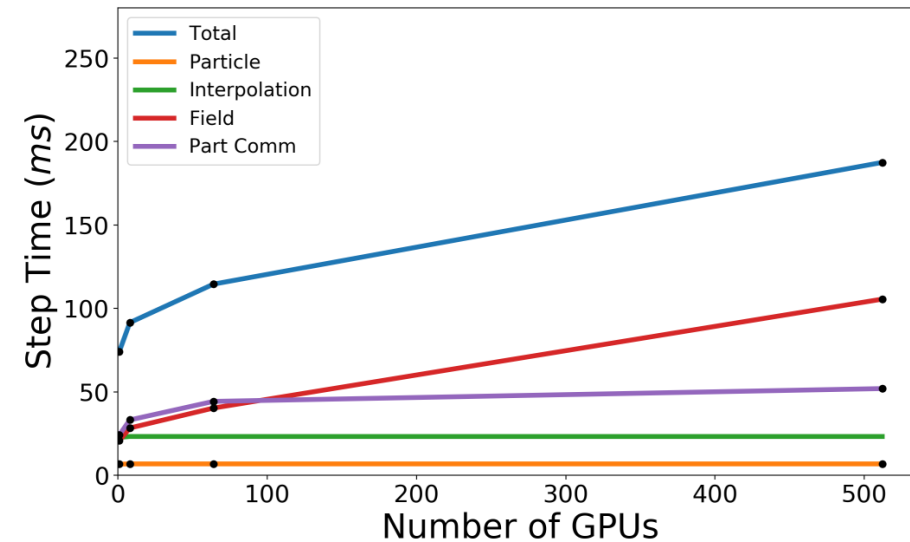
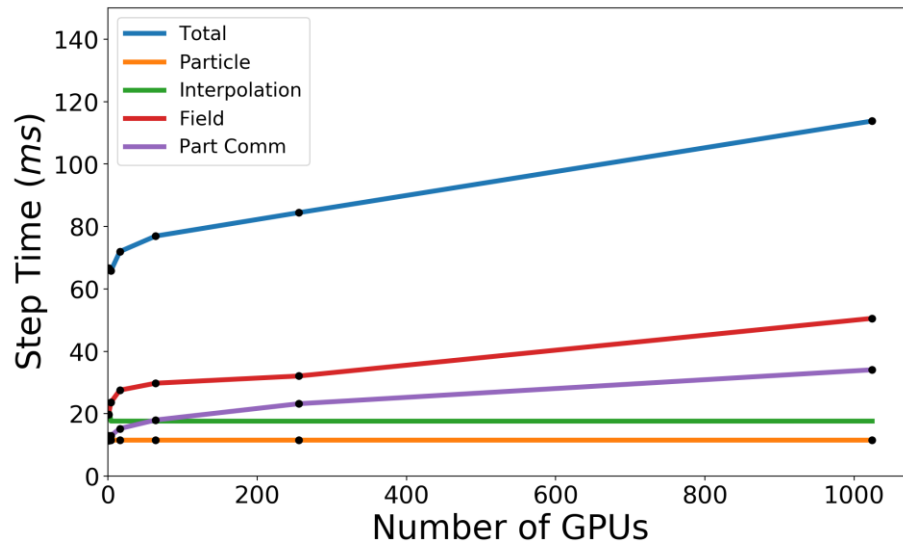


256<sup>2</sup> cells and  
1,000 particles-  
per-cell per GPU

3D



32<sup>3</sup> cells and  
1,000 particles-  
per-cell per GPU

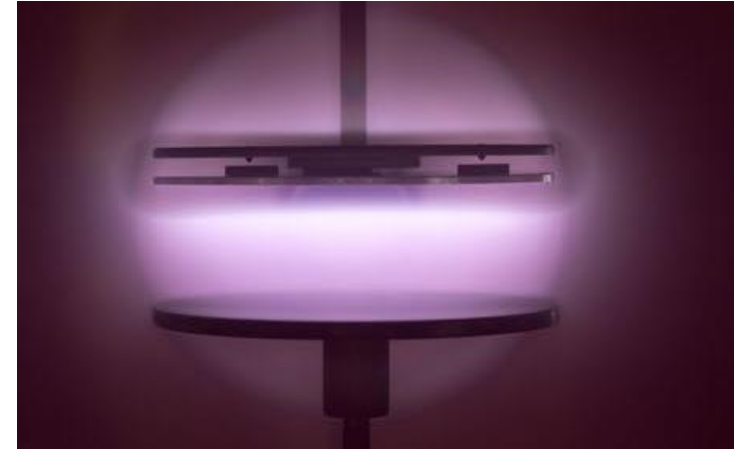


Domain x500 but efficiency decreases by only x1.5 = **large computational domain/geometry**

# Can we model the whole device?

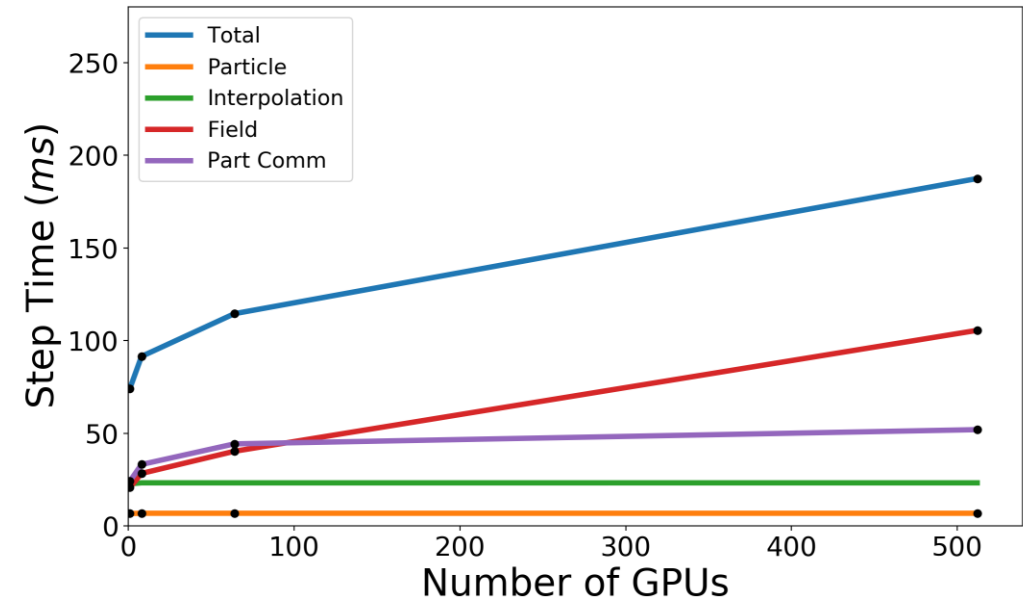
To model our etching device in 3D-3V, we require:

- $10^8$  cells ( $10 \times 10 \times 5 \text{ cm}^3$ )
- $10^{11}$  simulation particles
- $10^8$  time steps



Each time step is approximately  $100 \text{ ms}$  for a large 3D simulation

If we require  $10^8$  time steps this corresponds to a simulation  $> 100$  days!



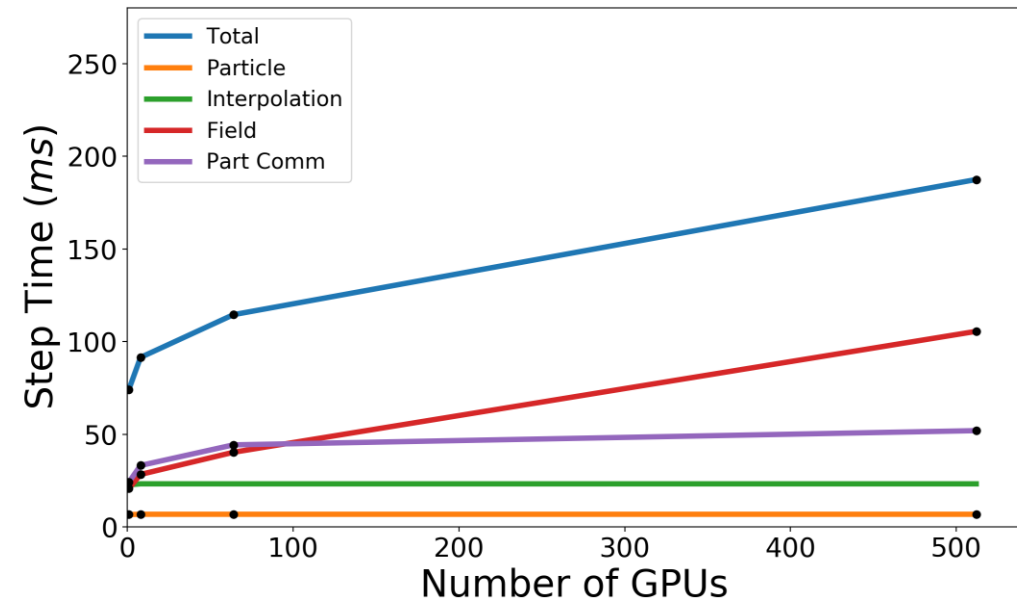
Weak scaling of LTP-PIC in 3D

# Can we model the whole device?

We think a goal of 10 days is potentially useful to industry

We can improve step time in three ways:

- More resources
- Better computer science
- **New algorithms**



Weak scaling of LTP-PIC in 3D

# Backup

# Talk Overview

1. Context and motivation
2. Modeling capabilities using EDIPIC-2D
3. Toward 3D whole-device modelling with LTP-PIC
4. Advanced algorithms

# 2D simulation of CCP

- 2D, 30 mTorr Argon discharge
- $4000 \times 1000$  cells,  $\approx 500$  particle-per-cell, 20 million time steps
- Simulated using 256 GPUs on the *Perlmutter* supercomputer in 6 days

Fig. Simulation geometry,

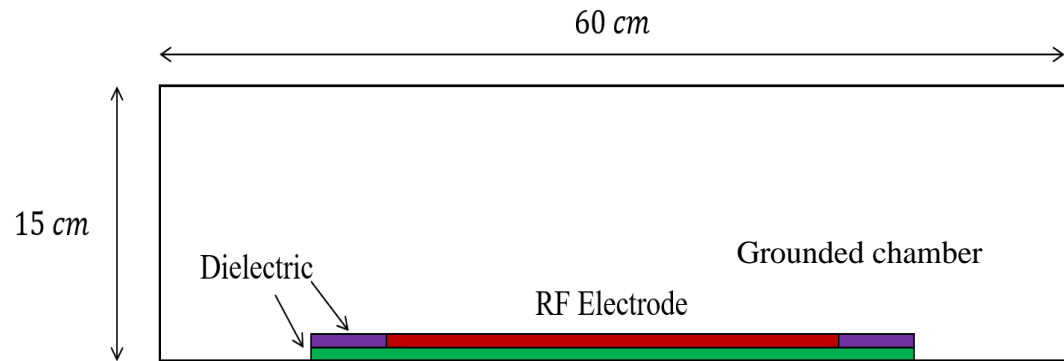
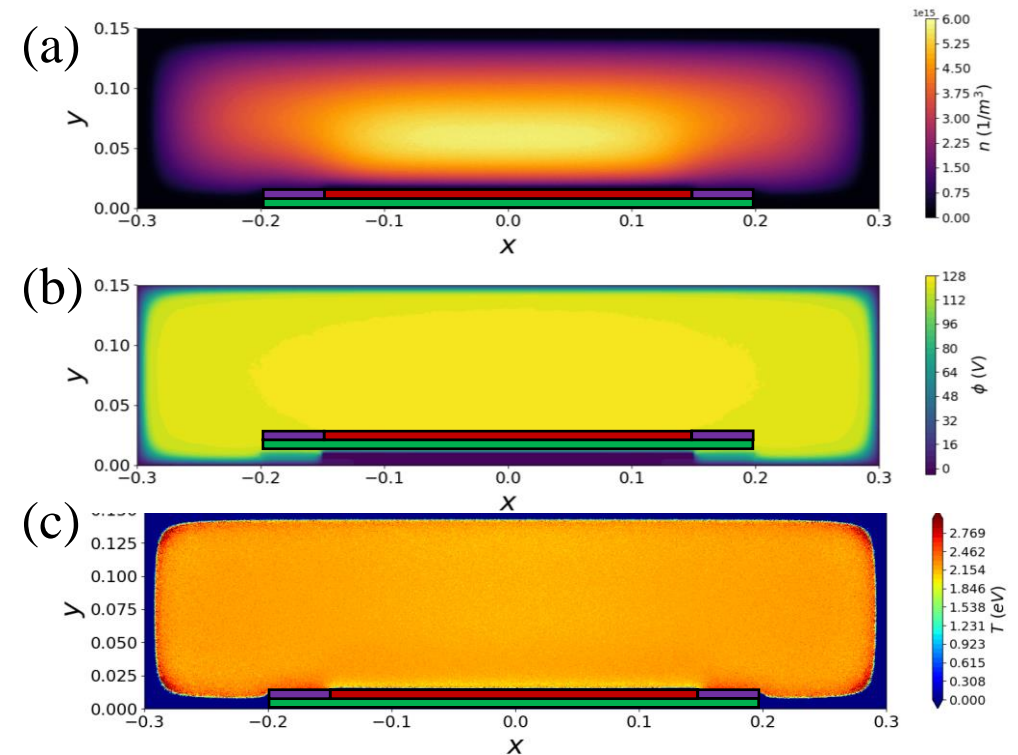
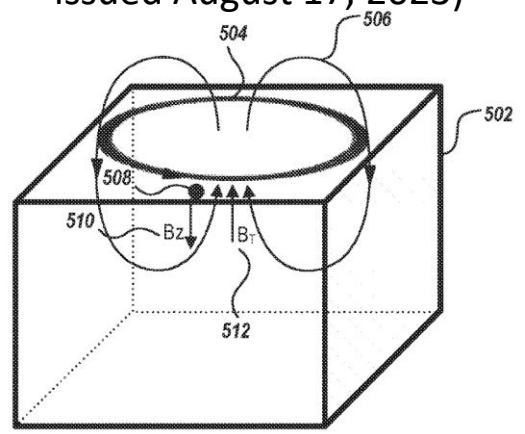


Fig. (a) Ion density, (b) plasma potential and (c) electron temperature at steady state

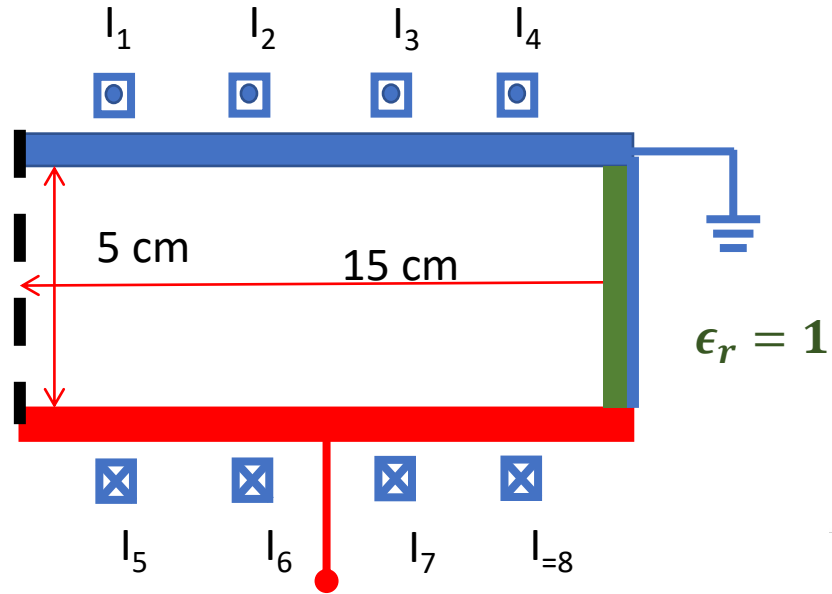


# Weakly magnetized CCP in cylindrical

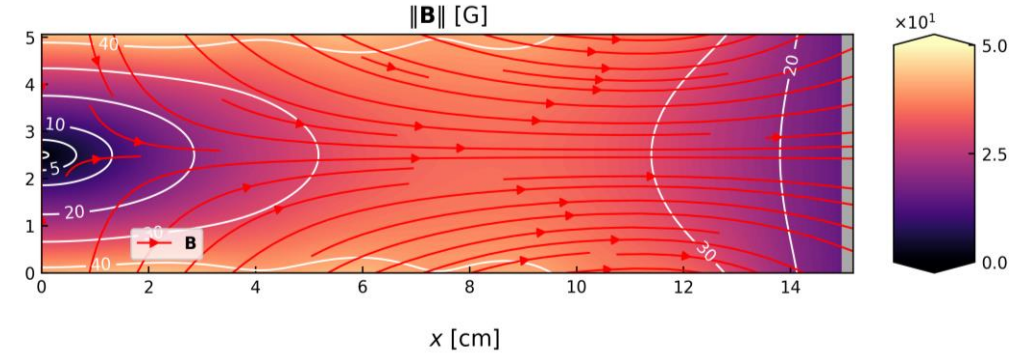
US Patent Application for  
PLASMA DISCHARGE  
UNIFORMITY CONTROL  
USING MAGNETIC FIELDS  
Patent Application  
(Application #20230260768  
issued August 17, 2023)



## CASE C (8 wires)



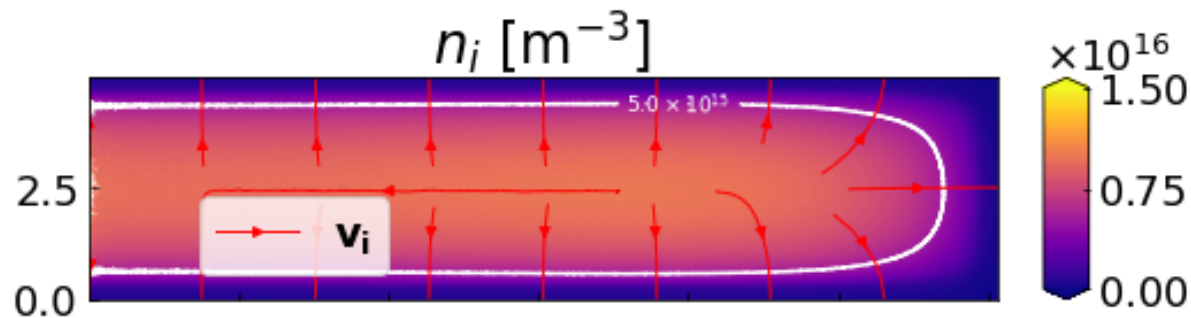
$$V = V_1 * \sin(2\pi f_1 t)$$



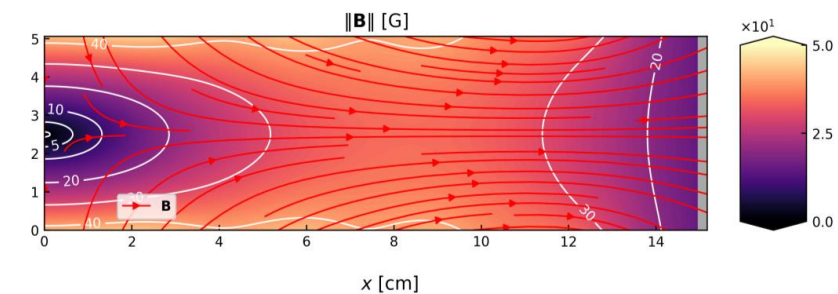
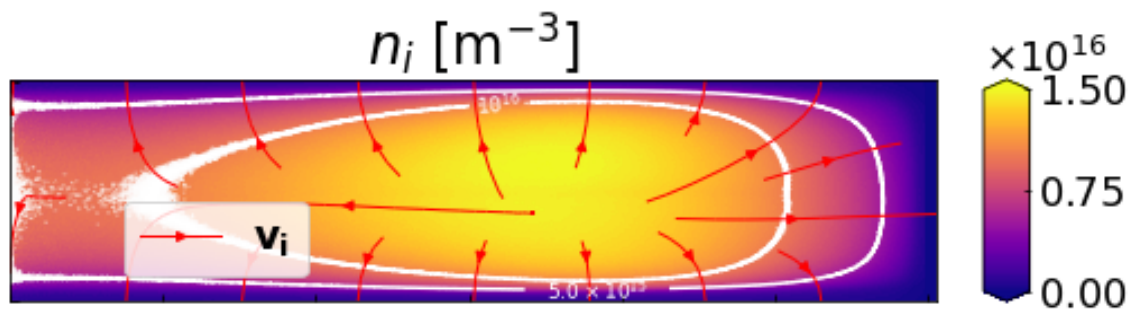


# Weakly magnetized CCP

Case A: no B field



Case C: eight loops



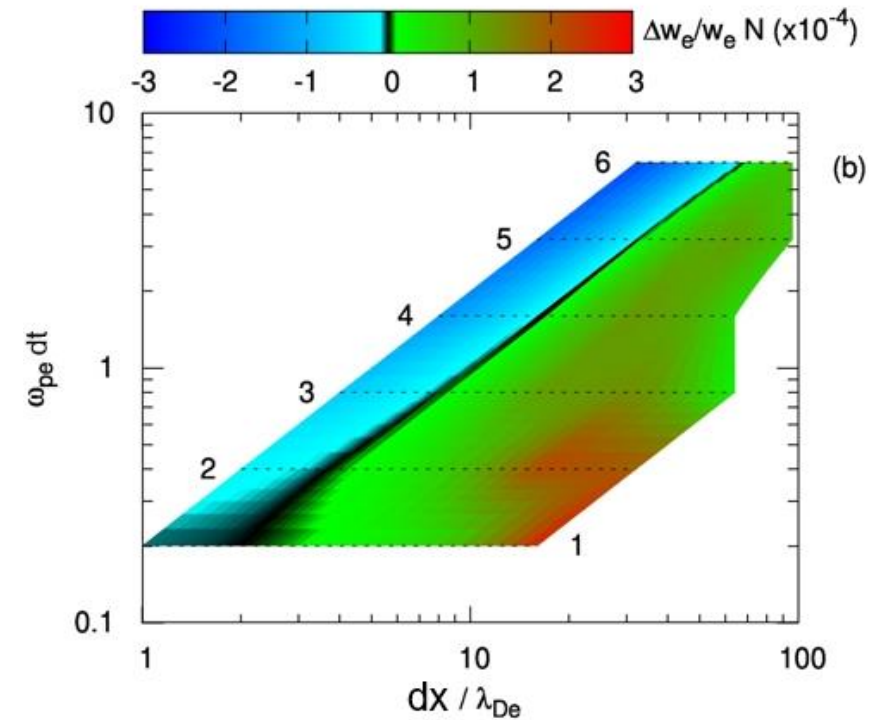
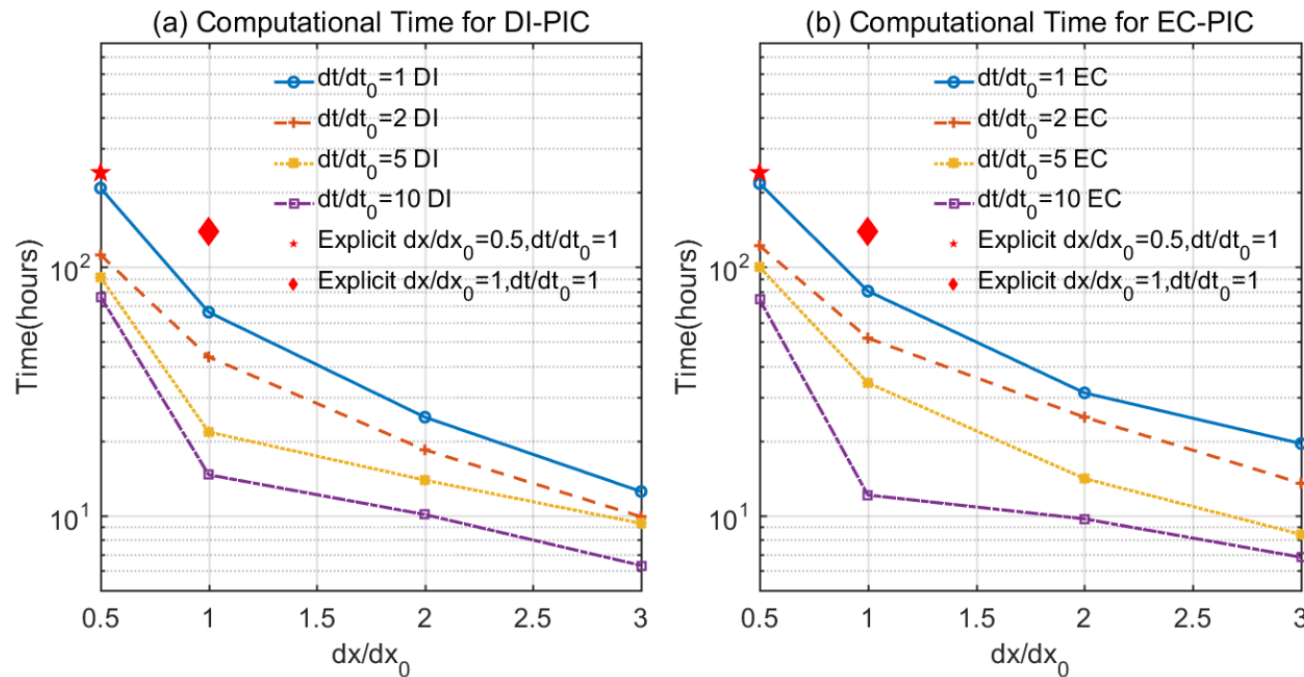
Plasma confinement where magnetic field is parallel to the walls

# Reducing the number of cells and time steps

Modeling a CCP system with alternative schemes:

**Direct Implicit** and **Energy Conserving**

Can obtain a significant speed up



<sup>1</sup> H. Sun, et al “Direct implicit and explicit energy-conserving particle-in-cell methods for modeling of capacitively coupled plasma devices,” *Physics of Plasmas* **30**(10), 103509 (2023).

Numerical heating or cooling in DI can be mitigated

## INDUSTRY

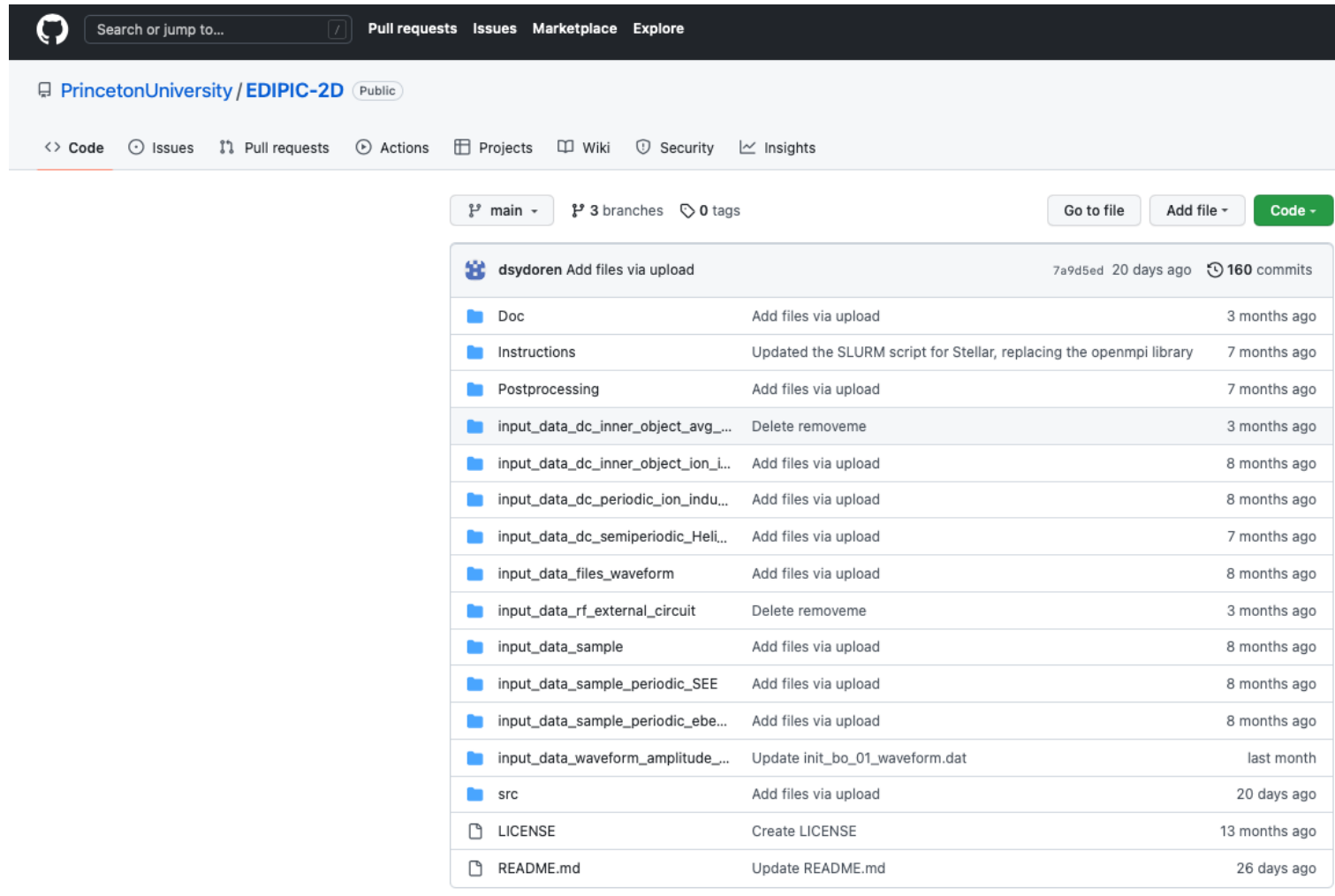
- Industry invests \$billions in large, complex machines for chip manufacturing (etching and deposition)
- Machines have limited diagnostics
- Fundamental research “takes too long” and is too expensive (prefer trial-and-error)
- However, industry recognizes the benefits that theoretical and computational research can bring

## MODELING NEEDS

- Fully **kinetic treatment** of low temperature plasmas (ICP, CCP, ECR, electron beam generated plasmas, hollow cathodes, dc and rf magnetrons, etc.)
- Complete reaction pathway of chemistry in the plasma and at the interface with surface
- Any insights on the plasma and chemical processes at play can give them a **huge advantage** over competition

# EDIPIIC: How to use?

Open source: public repository <https://github.com/PrincetonUniversity/EDIPIIC-2D>



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PrincetonUniversity / EDIPIIC-2D Public

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main 3 branches 0 tags Go to file Add file Code

File/Folder	Commit Message	Commit Date
dsydoren Add files via upload		7a9d5ed 20 days ago 160 commits
Doc	Add files via upload	3 months ago
Instructions	Updated the SLURM script for Stellar, replacing the openmpi library	7 months ago
Postprocessing	Add files via upload	7 months ago
input_data_dc_inner_object_avg_...	Delete removeme	3 months ago
input_data_dc_inner_object_ion_i...	Add files via upload	8 months ago
input_data_dc_periodic_ion_indu...	Add files via upload	8 months ago
input_data_dc_semiperiodic_Heli...	Add files via upload	7 months ago
input_data_files_waveform	Add files via upload	8 months ago
input_data_rf_external_circuit	Delete removeme	3 months ago
input_data_sample	Add files via upload	8 months ago
input_data_sample_periodic_SEE	Add files via upload	8 months ago
input_data_sample_periodic_ebe...	Add files via upload	8 months ago
input_data_waveform_amplitude_...	Update init_bo_01_waveform.dat	last month
src	Add files via upload	20 days ago
LICENSE	Create LICENSE	13 months ago
README.md	Update README.md	26 days ago

Unintended gas breakdowns in narrow gaps of advanced plasma sources for semiconductor fabrication industry

## Documentation:

- How to install on Stellar (or any clusters):  
[https://github.com/PrincetonUniversity/EDIPIIC-2D/blob/main/Instructions/installing\\_edipic2d.md](https://github.com/PrincetonUniversity/EDIPIIC-2D/blob/main/Instructions/installing_edipic2d.md)

- How to run on Stellar (or any clusters) from templates:  
[https://github.com/PrincetonUniversity/EDIPIIC-2D/blob/main/Instructions/running\\_edipic2d.md](https://github.com/PrincetonUniversity/EDIPIIC-2D/blob/main/Instructions/running_edipic2d.md)

## Installing EDIPIIC-2D

EDIPIIC-2D is a Fortran code so you need access to a Fortran compiler. The current makefile works with the Intel Fortran compiler as well as with GNU gfortran. The makefile determines which compiler is being used by looking at the output of the "mpifort -show" command (see MPI section below).

EDIPIIC-2D requires a few libraries in order to run. These are :

- MPI ([OpenMPI](#), [MPICH](#), [Intel-MPI](#), etc.)
- [PETSc](#)
- [HYPRE](#)
- BLAS/LAPACK

## Running EDIPIIC-2D

The easiest way to get started with EDIPIIC-2D is by copying one of the examples found in the top directory of the repository and modifying it to match the parameters of your system. The example directories are:

- [input\\_data\\_sample](#)
- [input\\_data\\_sample\\_periodic\\_SEE](#)
- [input\\_data\\_sample\\_periodic\\_ebeam](#)
- [input\\_data\\_files\\_waveform](#)

# EDIPIIC: How to use?

## Documentation:

- How to post process data:
  - Via gnuplot
  - Via python scripts

[https://github.com/PrincetonUniversity/EDIPIIC-2D/blob/main/Doc/EDIPIIC2D\\_output\\_data\\_description\\_0.pdf](https://github.com/PrincetonUniversity/EDIPIIC-2D/blob/main/Doc/EDIPIIC2D_output_data_description_0.pdf)

- Code overview and input file description:

<https://github.com/PrincetonUniversity/EDIPIIC-2D/tree/main/Doc>

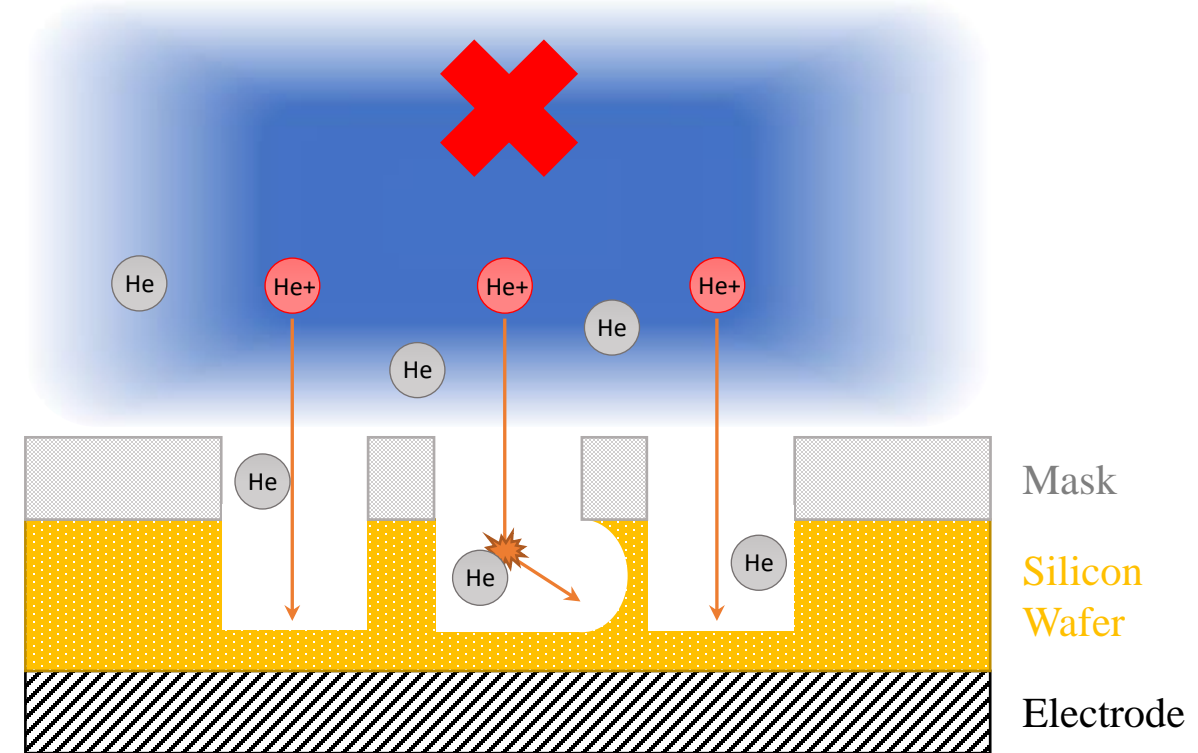
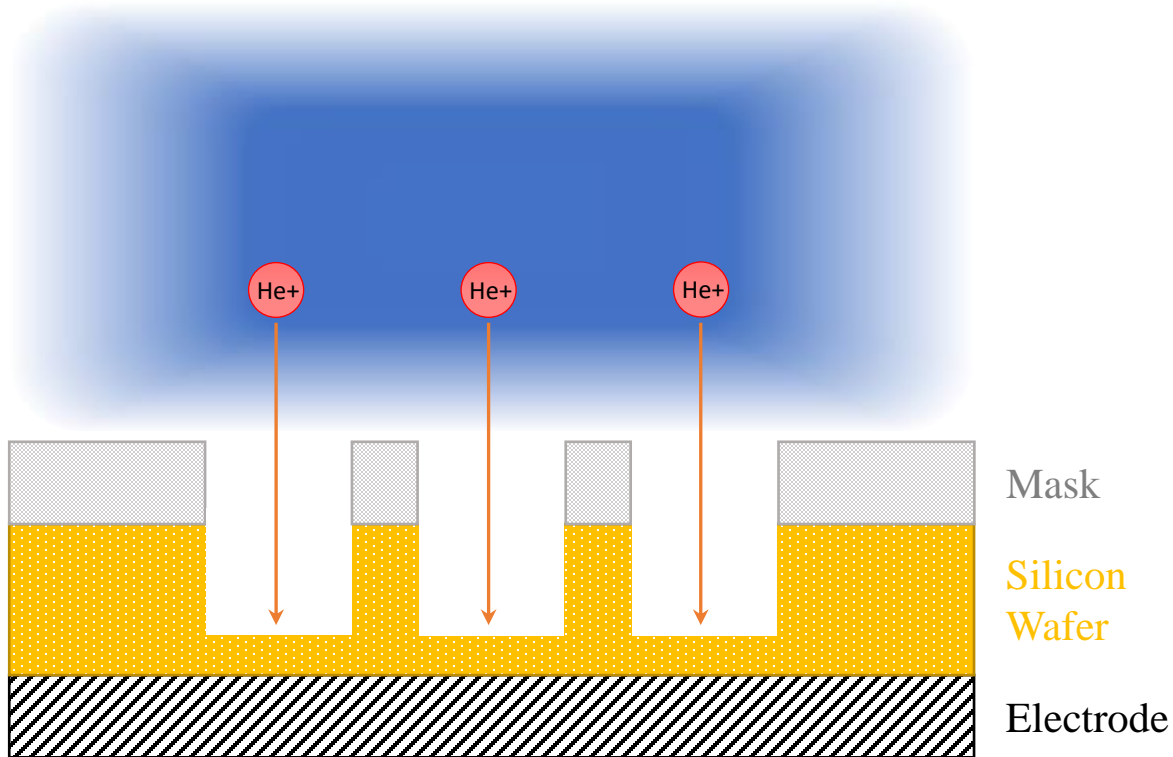
- And we can help!



# Low-pressure plasma modelling challenges

A low-pressure plasma is essential to maintain ion etch *anisotropy*

At higher pressures, the ions may collide with particles on their way to the surface deflecting their velocity vector



# Low-pressure plasma modelling challenges



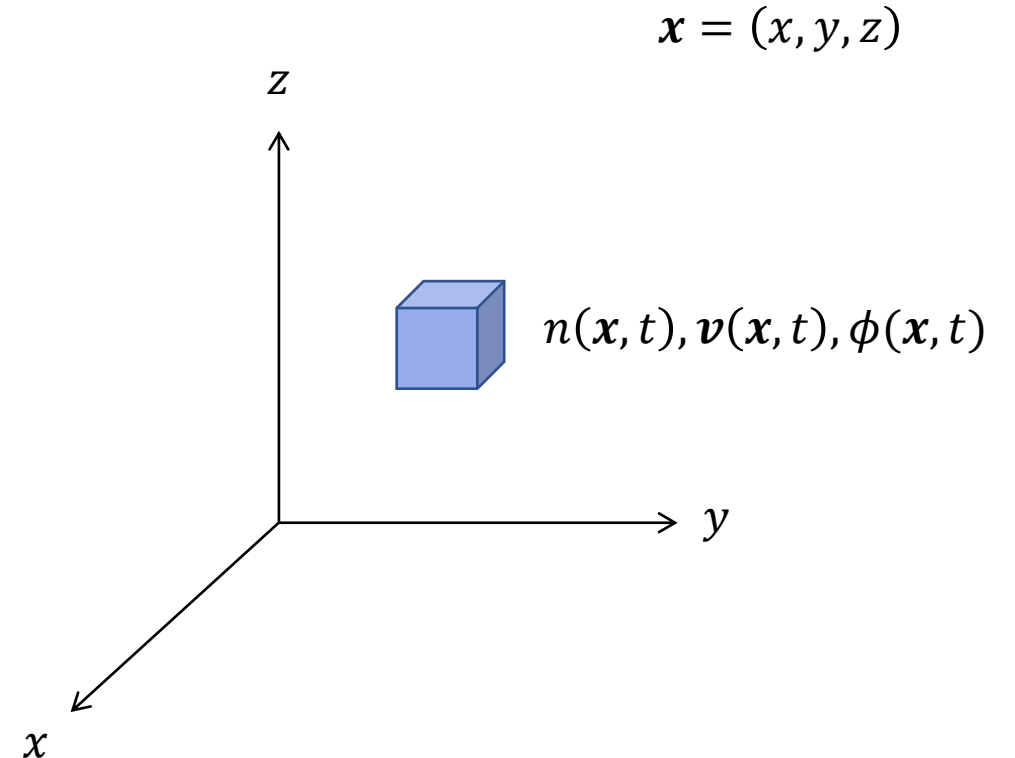
Often in gas or plasma simulations we rely on a **fluid** treatment

$n(\mathbf{x}, t)$  – Number density

$\mathbf{v}(\mathbf{x}, t)$  – Velocity vector

And if the plasma is electrostatic we can solve for:

$\phi(\mathbf{x}, t)$  – Electric potential



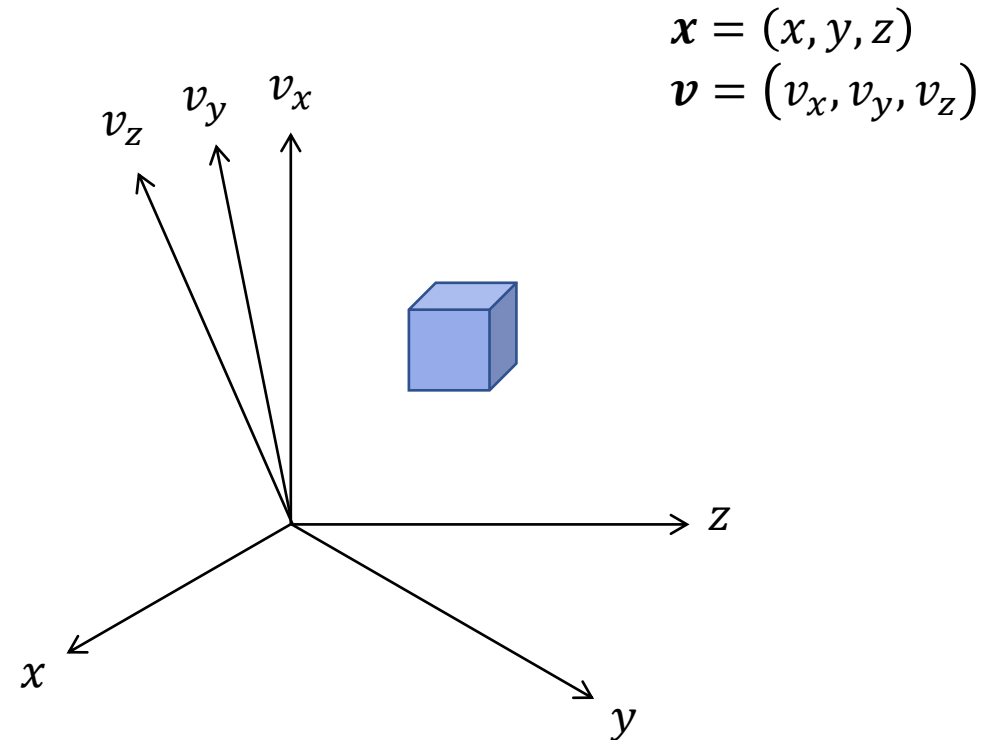


# Low-pressure plasma modelling challenges

However, we are considering a *low-pressure* system, where our gas/plasma is weakly collisional

In this case we cannot assume that our plasma has a Maxwellian velocity distribution.

The fluid approximation breaks down and we must use a six-dimensional ***kinetic*** treatment

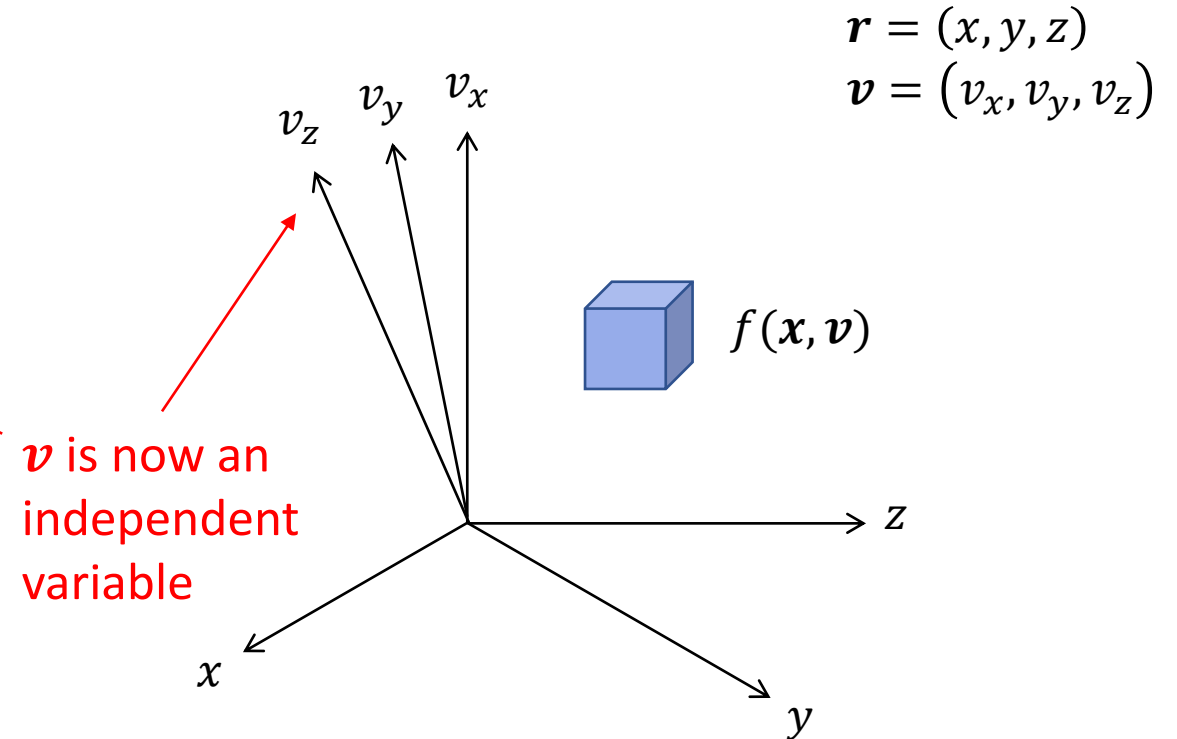


Kinetic plasma equations:

$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \frac{\partial f}{\partial \mathbf{x}} - \frac{q}{m} \frac{\partial \phi}{\partial \mathbf{x}} \cdot \frac{\partial f}{\partial \mathbf{v}} = 0$$

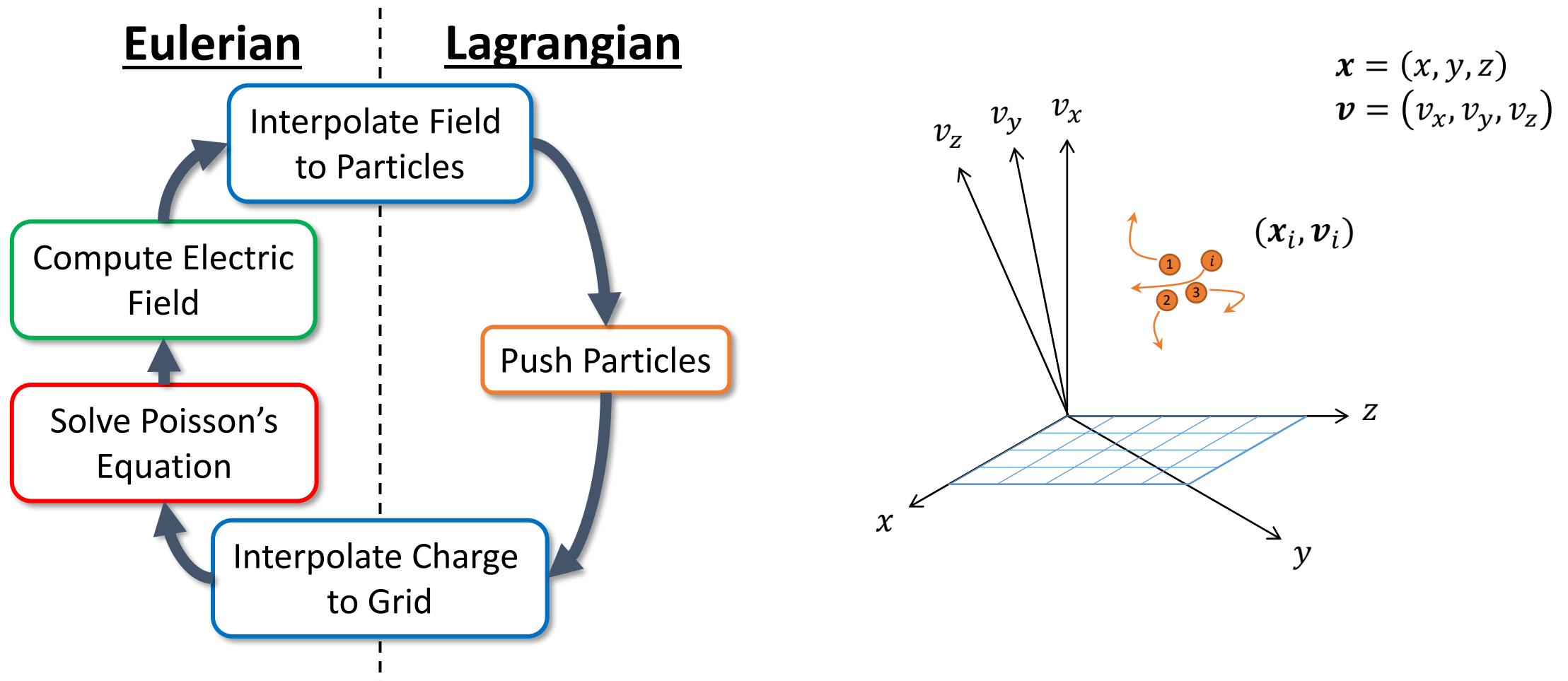
With the Poisson equation:

$$\epsilon_0 \frac{\partial^2 \phi}{\partial \mathbf{x}^2} = -q \int f d\mathbf{v}$$



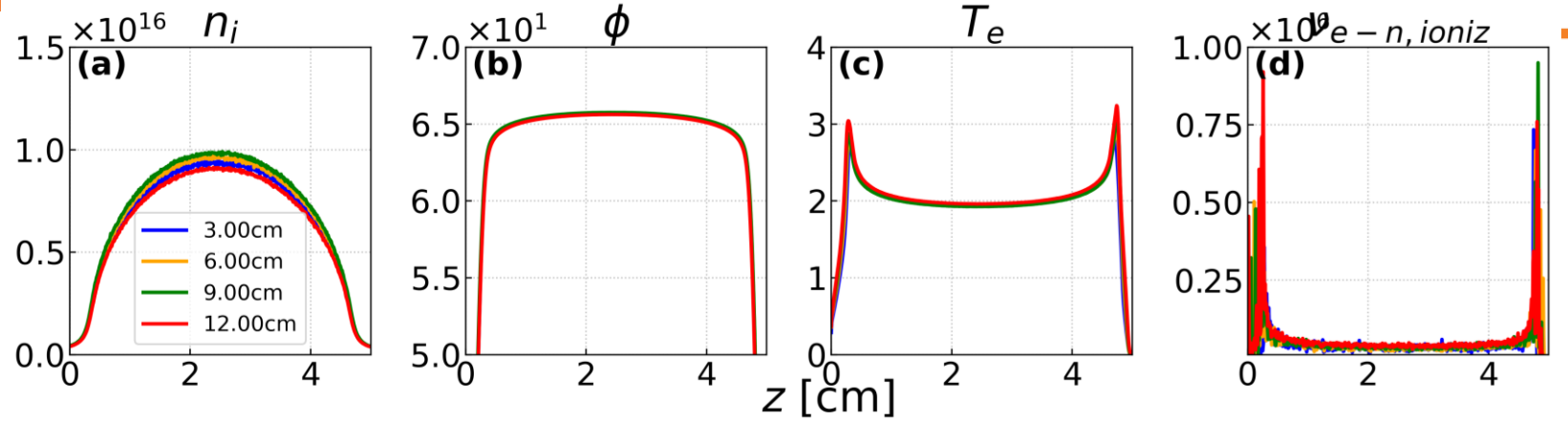
# Low-pressure plasma modelling challenges

Solve kinetic equation via Particle-In-Cell simulations

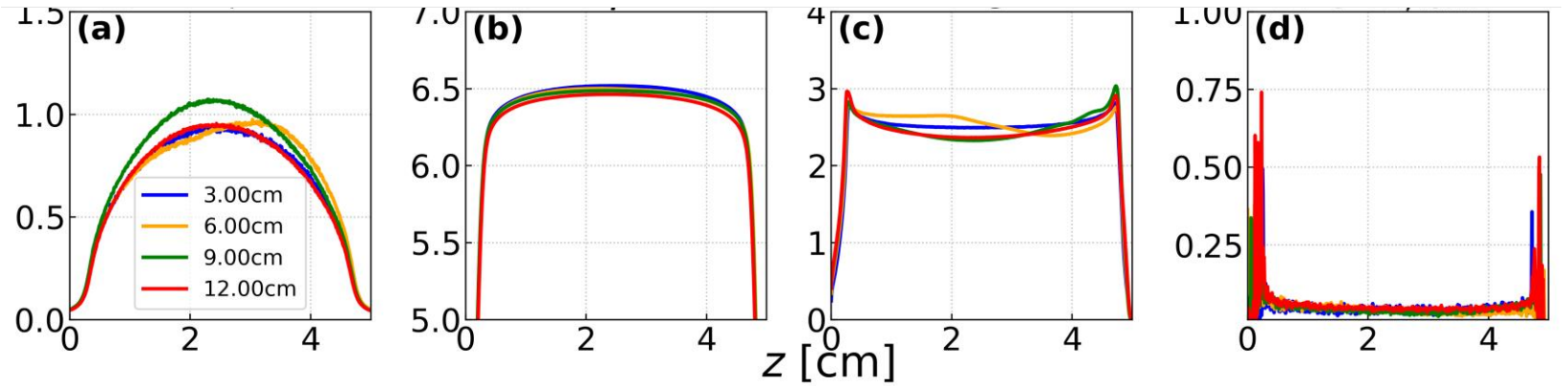


# 1D cuts at radial locations

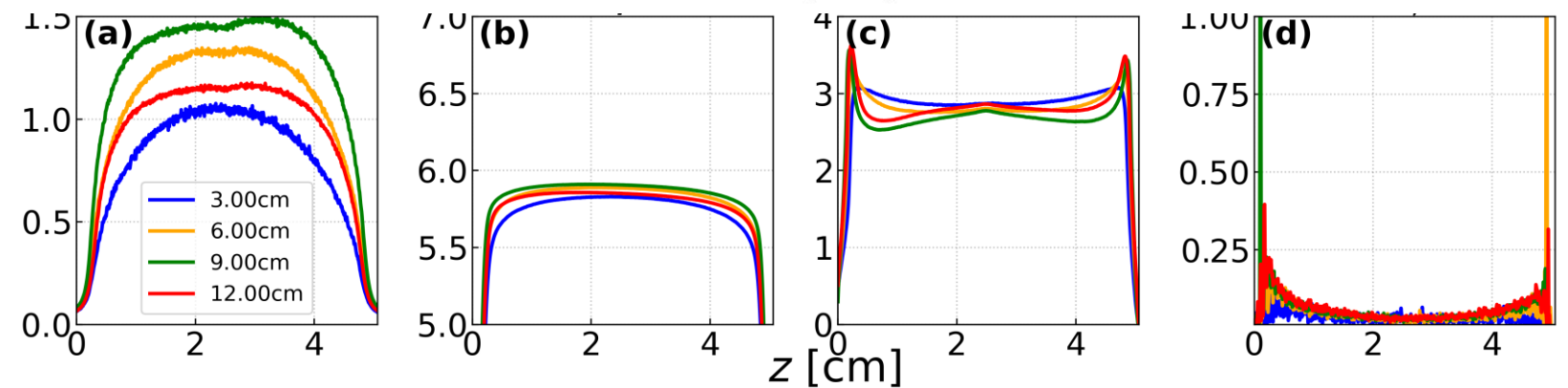
Case A: no B field



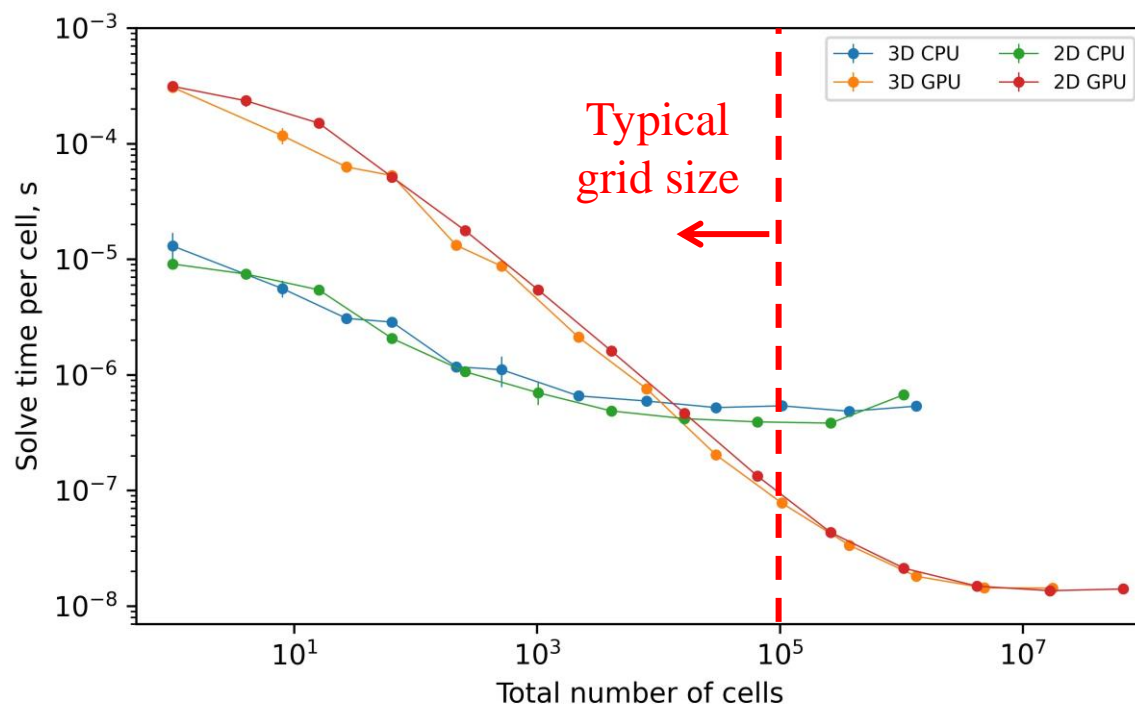
Case B: one loop



Case C: eight loops



# Accelerating LTP-PIC with *OpenACC*



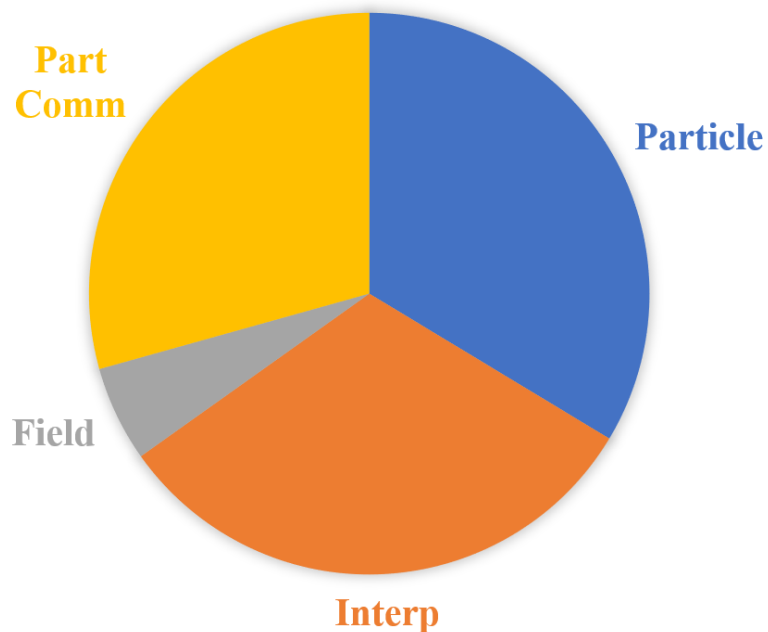
Assume, on a single GPU,  $\sim 10$  GB per plasma species:

- This allows us to model around  $10^8$  particles, per-species, per-GPU
- Corresponding to around  $10^5$  cells per-GPU

Such a grid is not big enough to take full advantage of the GPU

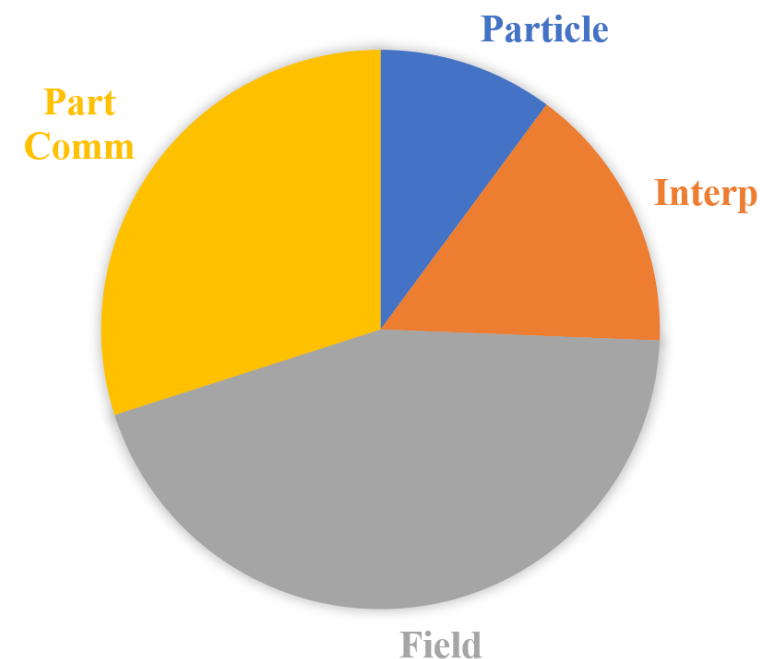
# Accelerating LTP-PIC with *OpenACC*

64 CPU



2D simulations  
modelling  $8,192^2$   
cells with 1,000  
particles-per-cell

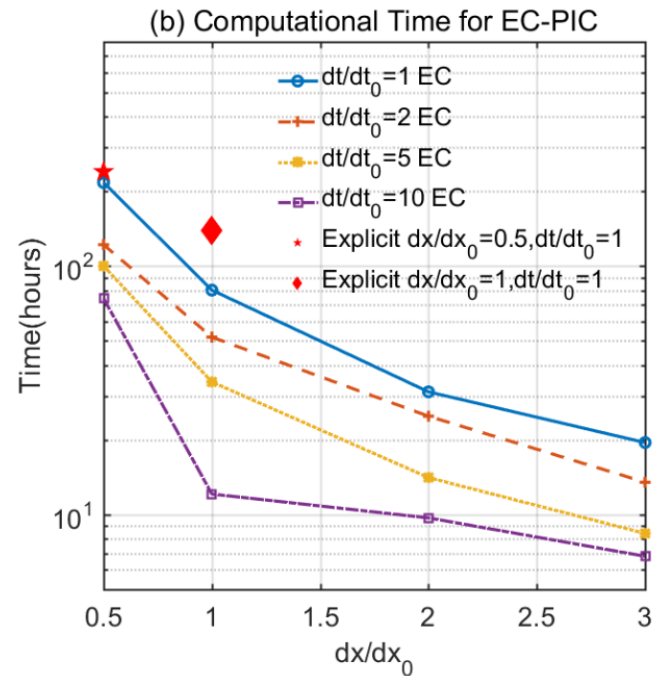
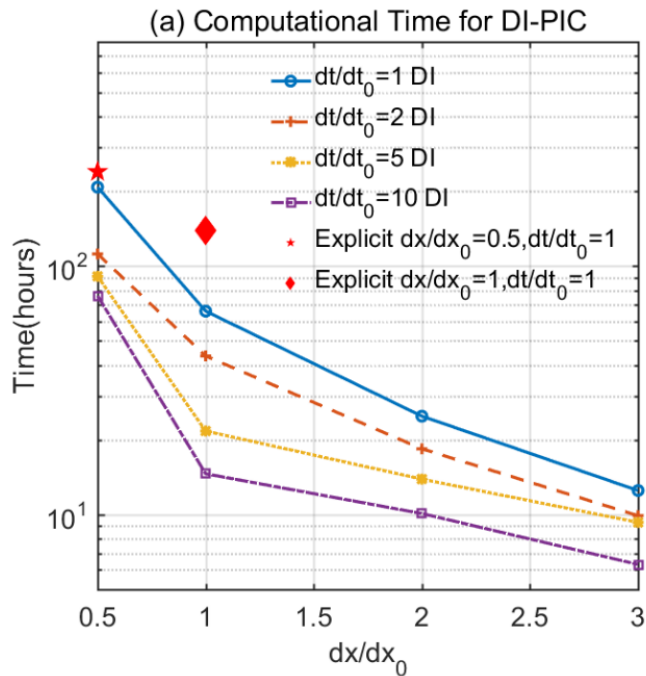
4 CPU + 4 GPU



# Reducing the number of cells and time steps

Modeling a CCP system with alternative schemes [1]:

**Direct Implicit** and **Energy Conserving**



Can obtain a significant **speed up x10**  
Simulations were verified with a classic  
momentum conserving explicit PIC  
schemes

<sup>1</sup> H. Sun, et al "Direct implicit and explicit energy-conserving particle-in-cell methods for modeling of capacitively coupled plasma devices," *Physics of Plasmas* **30**(10), 103509 (2023).

# Reducing the number of cells and time steps

Energy conserving test on 1D CCP benchmark [1]



Non uniform grid at the sheaths

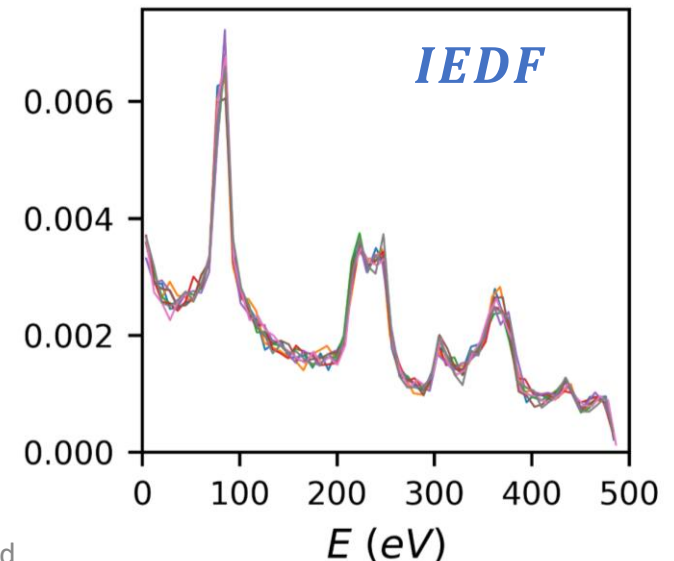
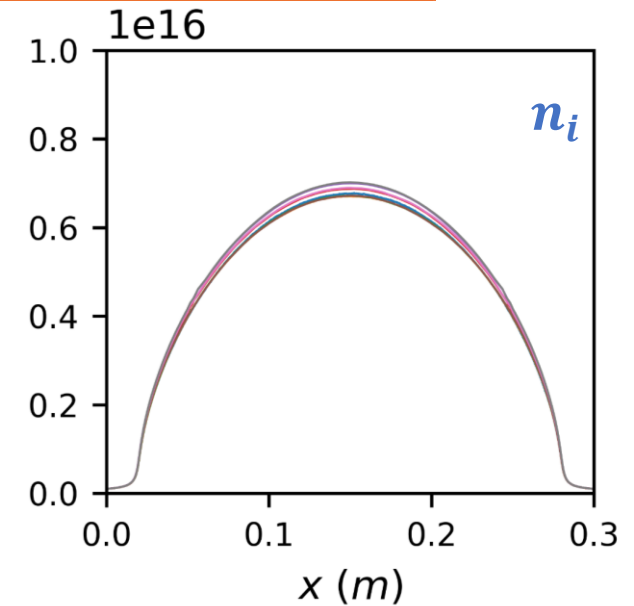
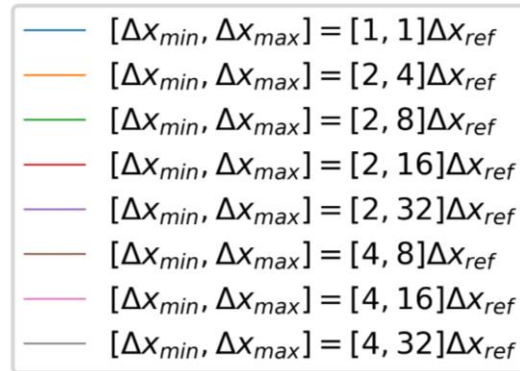


For the lowest resolution case 1-norm error of:

**Ion density 4.3%.**

**Electron temp 5.1%.**

**This corresponds to a 10x reduction in number of cells [2].**



[1] M.M. Turner, et al, "Simulation benchmarks for low-pressure plasmas: Capacitive discharges," Physics of Plasmas **20**(1), 013507 (2013).

[2] Preprint available at [arXiv:2308.13092](https://arxiv.org/abs/2308.13092)